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Mechanisms in Materials**

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**MD simulation of interaction between radiation damages and microstructure:  
voids, helium bubbles and grain boundaries**

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# **MD simulation of interaction between radiation damages and microstructures: voids, helium bubbles and grain boundaries**

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# Collaboration

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*Kharkov Institute of Physics and Technology, Ukraine*

**Robin Schäublin**

*EPFL SB CRPP Groupe Matériaux, PSI, Switzerland*



# Motivation

## Rate theory

J. L. Katz, H. Wiedersich, J. Chem. Phys. 55 (1971) 1414-1425

A. D. Brailsford, R. Bullough, J. Nucl. Mater. 44 (1972) 121-135

$$dC_i/dt = G_i - \alpha_{iv}C_iC_v - \kappa_i D_i C_i + \nabla \left( D_i \nabla C_i + \frac{D_i C_i}{kT} \nabla U_i \right) \quad \kappa_i = \sum_j \kappa_i^j$$

$$dC_v/dt = G_v - \alpha_{iv}C_iC_v - \kappa_v D_v C_v + \nabla \left( D_v \nabla C_v + \frac{D_v C_v}{kT} \nabla U_v \right) \quad \kappa_v = \sum_j \kappa_v^j$$

$j = \text{voids, dislocations, grain boundaries etc}$

$$D_{i,v} = D_{i,v}^0 \exp(-E_{i,v} / kT) \quad \alpha_{iv} = 4\pi r_{iv} (D_i + D_v)$$

It is assumed that under irradiation, Frenkel pairs of vacancies and SIAs are created in the bulk and annihilated at extended defects, such as dislocations, grain boundaries, cavities and the like, which are thus considered primarily as the *sinks* for point defects. However, extended defects can act also as the **radiation-induced sources** of point defects, which can result in a new driving force of the microstructural evolution.

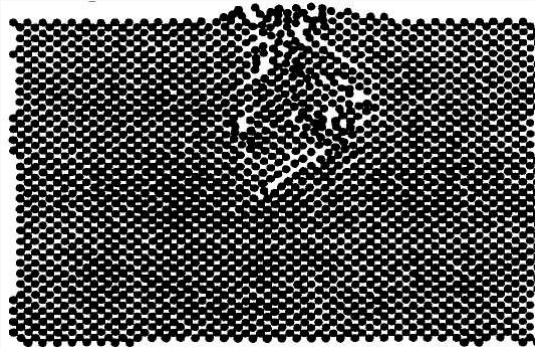
# Motivation

Favored formation of vacancies close to extended defects observed by simulation of collision cascade development near

## External surface

10 keV, Au

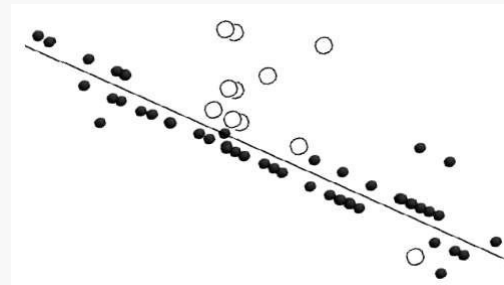
M. Ghaly and R.S. Averback,  
Phys. Rev. Lett. 72 (1994) 364.



## Bilayer interfaces

5 keV, Co/Cu

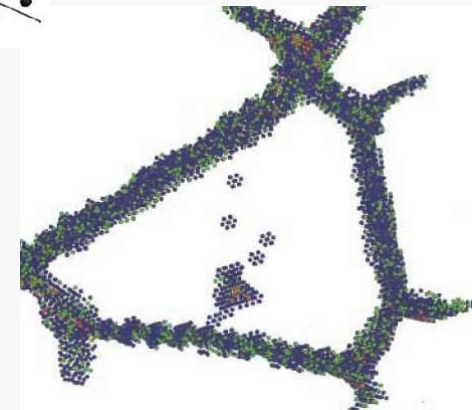
K. Nordlund and R. S. Averback,  
Phys. Rev. B59 (1999) 20.



## Grain boundaries

20 keV, Ni

M. Samaras, P. M. Derlet, H. Van Swygenhoven,  
M. Victoria, Phys. Rev. Lett. 88 (2002) 125505.





# Motivation

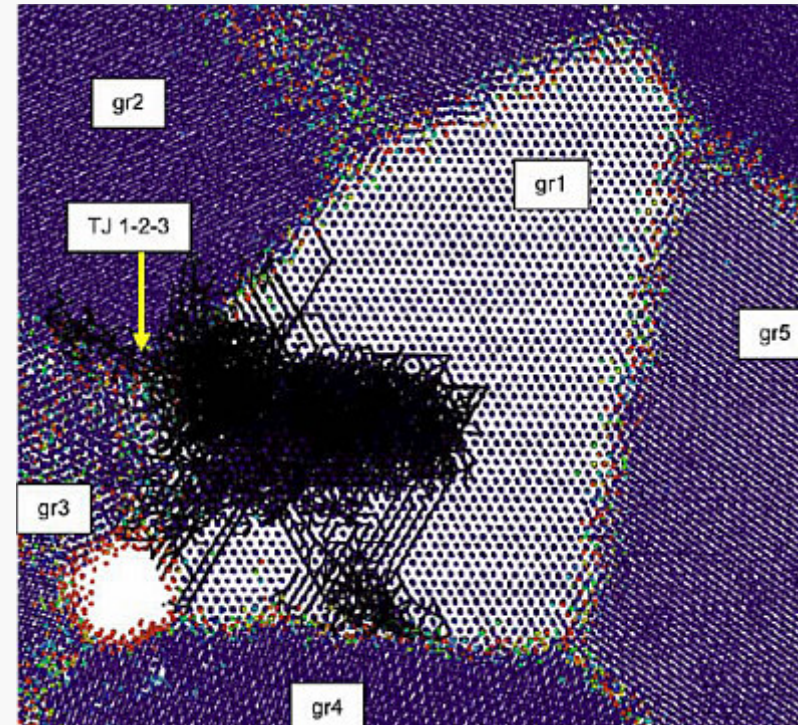
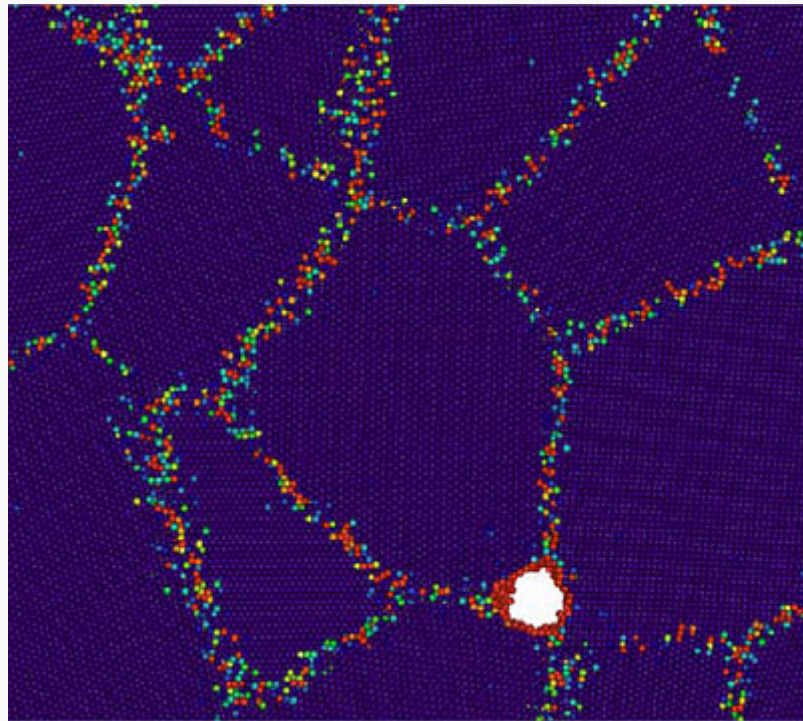
Kai Nordlund et al, Nature 398 (1999) 6722

Damage production in bulk and surface events:

	<u>Vacancies</u>		<u>Interstitials</u>	
	<b>Ave.</b>	<b>Max</b>	<b>Ave.</b>	<b>Max</b>
<b>Cu bulk.</b>	<b><math>32 \pm 7</math></b>	<b>59</b>	<b><math>35 \pm 11</math></b>	<b>77</b>
<b>Cu surf.</b>	<b><math>240 \pm 50</math></b>	<b>388</b>	<b><math>32 \pm 9</math></b>	<b>77</b>
<b>Ni bulk</b>	<b><math>26 \pm 12</math></b>	<b>71</b>	<b><math>31 \pm 7</math></b>	<b>57</b>
<b>Ni surf.</b>	<b><math>38 \pm 6</math></b>	<b>52</b>	<b><math>27 \pm 6</math></b>	<b>56</b>

# Motivation

M. Samaras, W. Höffelner, M. Victoria, J. Nucl. Mat. 352 (2006) 50–56



Simulation of a pre-existing void in nc bcc Fe indicates that the void plays a role as a sink to self interstitial atoms during displacement cascades.



# Outline

- Defect production close to voids in Cu at low energy cascades
- Diffusion and primary damages in Fe
- Biased defects creation near voids in Fe at high energy cascades
- Simulation of point defects production near helium bubbles
- Recrystallization processes under irradiation





## Simulation method

### Molecular Dynamics with Empirical force-field

EAM potential: 
$$U = \sum_{ij} V(r_{ij}) + \sum_i F(\bar{\rho}_i), \quad \bar{\rho}_i = \sum_j \phi(r_{ij})$$

#### Parameterization:

**Cu:** Yu. Mishin et al, *Phys. Rev.*, B 63 (2001) 224106.

**Fe:** M.I. Mendeleev et al, *Phil. Mag.* 83 (2003) 3877–94.

**He:** D.E. Beck D.E. *Mol. Phys.* 14 (1968) 311.

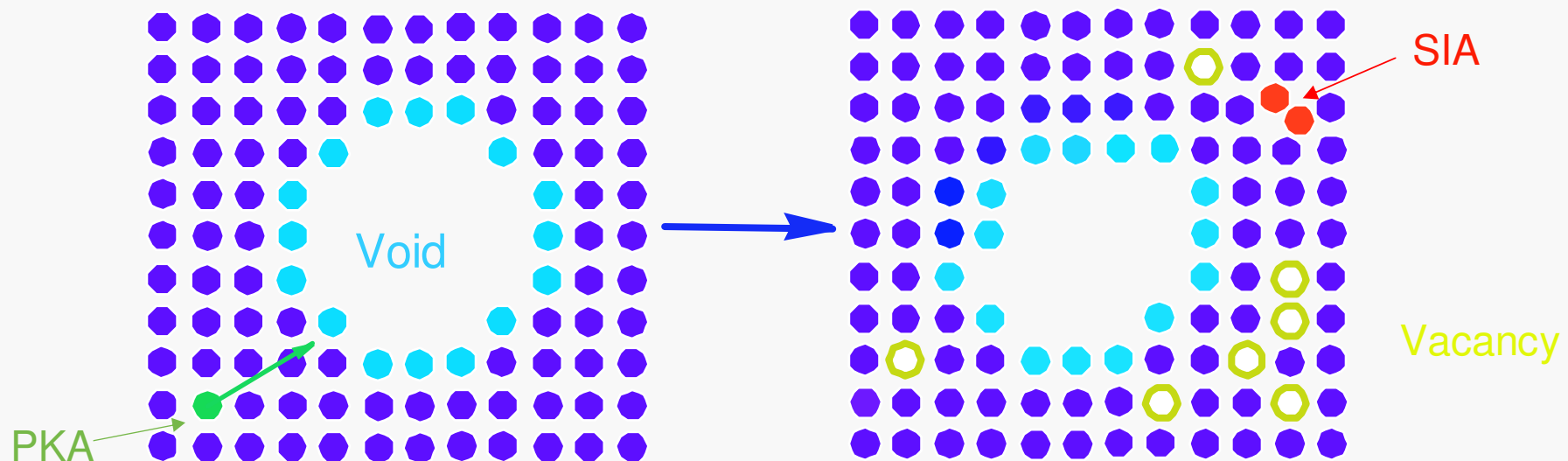
**Fe–He:** N. Juslin, K. Nordlund, *J. Nucl. Mater.* 382 (2008) 143.

# Defect production close to voids in Cu

N. P. Lazarev, V. I. Dubinko, Radiat. Eff. & Def. Solids 158 (2003) 803.

V.I. Dubinko, N.P. Lazarev, Nucl. Instr. Meth. Phys. Res. B 228 (2005) 187

The initial sizes of voids are varied from 312 to 1004 atomic volumes.  
PKAs are generated at about 3-5 atomic distances from the void.

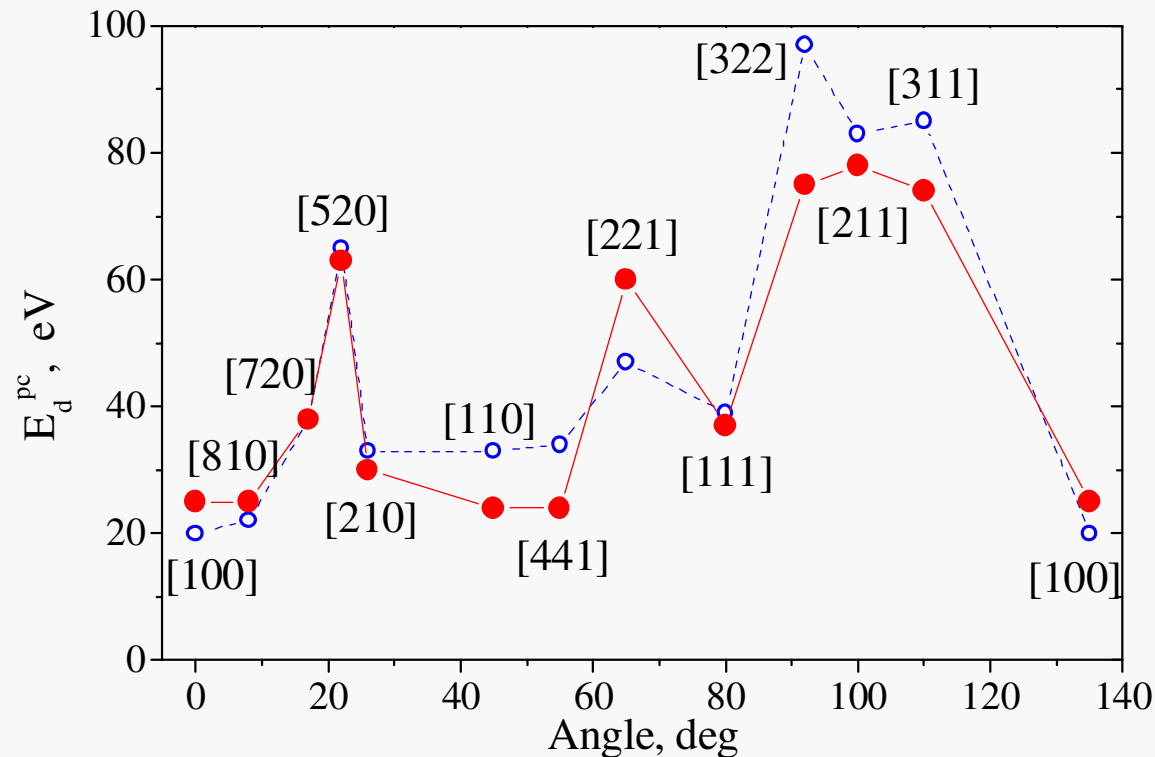


*The collision events close to voids results in a biased formation of vacancies due to the lower energy barrier involved*

# Displacement threshold energy in bulk Cu at $T = 4$ K

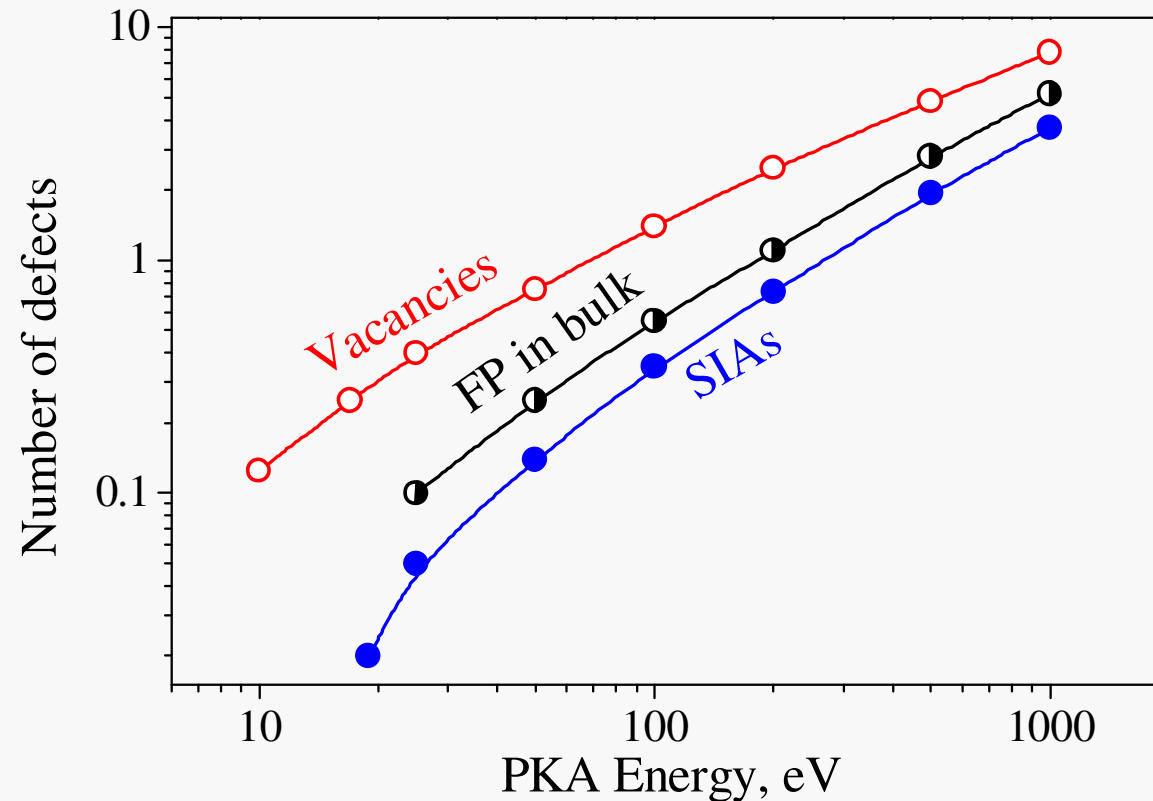
N. P. Lazarev, V. I. Dubinko, Radiat. Eff. & Def. Solids 158 (2003) 803.

D. J. Bacon, H. F. Deng, F. Gao, J. Nucl. Mater. 205 (1993) 84.



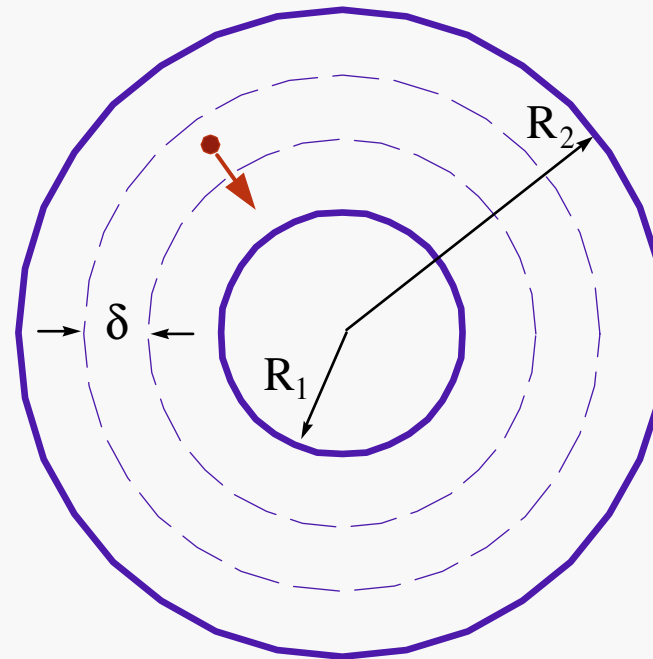
*The lowest threshold energy is about 25 eV. PKA in the direction close to  $\langle 110 \rangle$  generates replacement collision sequence and produce stable Frenkel defects separated by large distances starting from  $l = 4$  at 24 eV to tens inter-atomic distances at higher energies.*

## A biased formation of vacancies in the vicinity of void



The ratio  $N_v / N_i$  amounts to about 8 at 25 eV and decreases to  $\sim 2$  at 1 keV. The effect decreases with increasing distance from the void surface.

## Simulation of void dissolution by subthreshold irradiation



Schematic picture of void inside solid sphere. PKA ranges in between of two spheres depicted by dotted lines.

Initial sizes:  $R_1 = 15 \text{ \AA}$ , and  $R_2 = 45 \text{ \AA}$ .  $N = 31872$  atoms.

Every about 35 ps a new collision with  $E_K = 18 \text{ eV}$  was generated.



## Time of thermal dissolution of void

$$dV/dt = 4\pi D_v R (\bar{C}_v - C_v^b) \quad C_v^b = C_v^0 \exp(2\gamma/R) \quad \gamma = \sigma\omega/kT$$

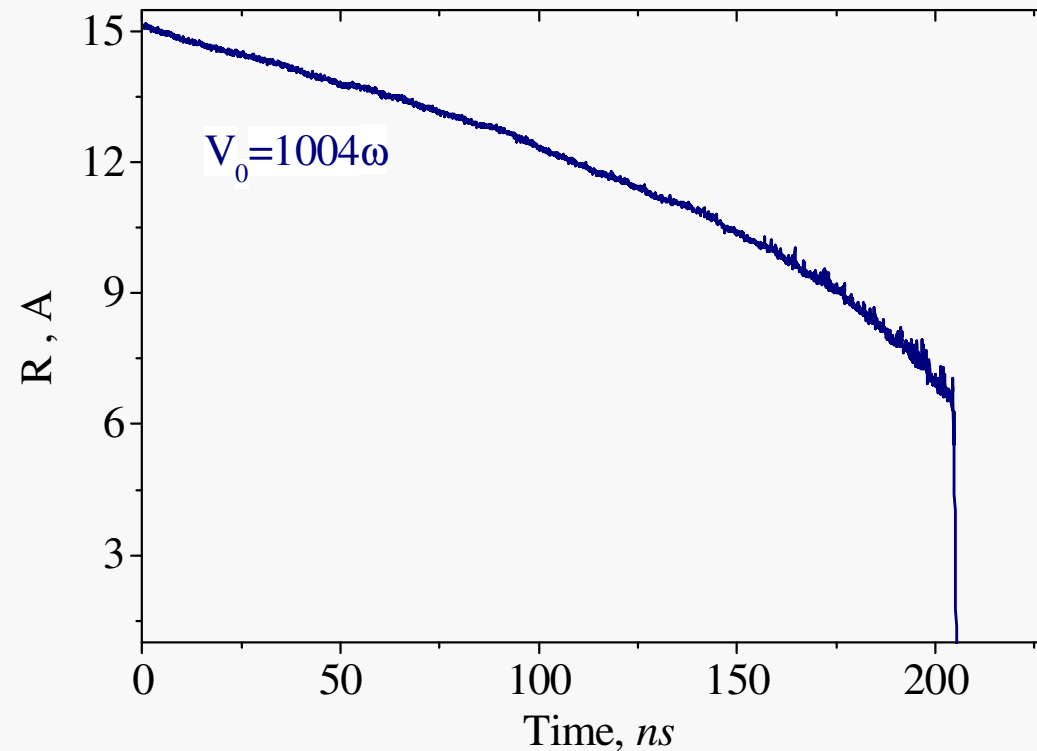
$$dR/dt = (1 - \exp(2\gamma/R)) D_v C_v^0 / R$$

$$\tau_{th} = \frac{R_0^3}{2\gamma D_v C_v^0 (2 + \exp(2\gamma/R_0))}$$

At  $T = 1000$  K,  $R_0 = 15$  Å, energetic parameters of Cu, the estimated time  $\tau_{th}$  is about 0.3 ms which is far above the time accessible in usual MD simulations

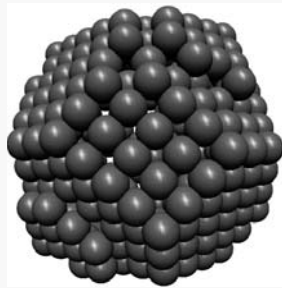
## Time dependence of void size during irradiation

$T = 1000 \text{ K}$   
 $E_K = 18 \text{ eV}$   
>5000 cascades

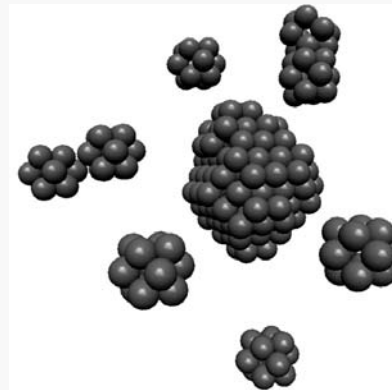


*The void has been dissolved completely: at  $R = 6 \text{ \AA}$ , the void has been transformed to a stacking fault tetrahedron.*

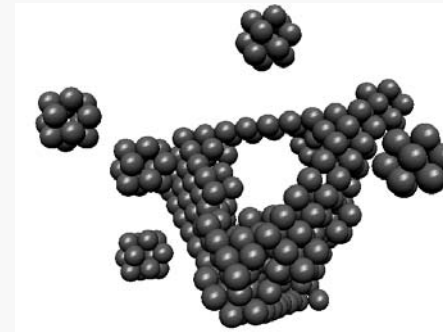
## Different stages of void dissolution



Initial void



Dissolved void  
after ~200 ns



Beginning of SFT  
formation



Final state of SFT  
development



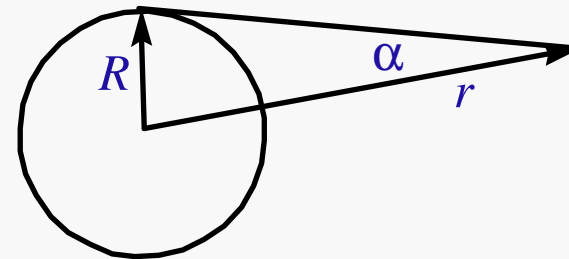
## Void dissolution rate due to radiation emission of vacancies

Only PKAs directed towards the void create vacancies.

Vacancy generation rate:

$$K^*(r, R) = \frac{K(r, R)}{2} \left[ 1 - \sqrt{1 - \frac{R^2}{r^2}} \right]$$

$$K(r, R) = \begin{cases} K_0, & R < r < R + \Delta \\ 0, & \text{otherwise} \end{cases}$$



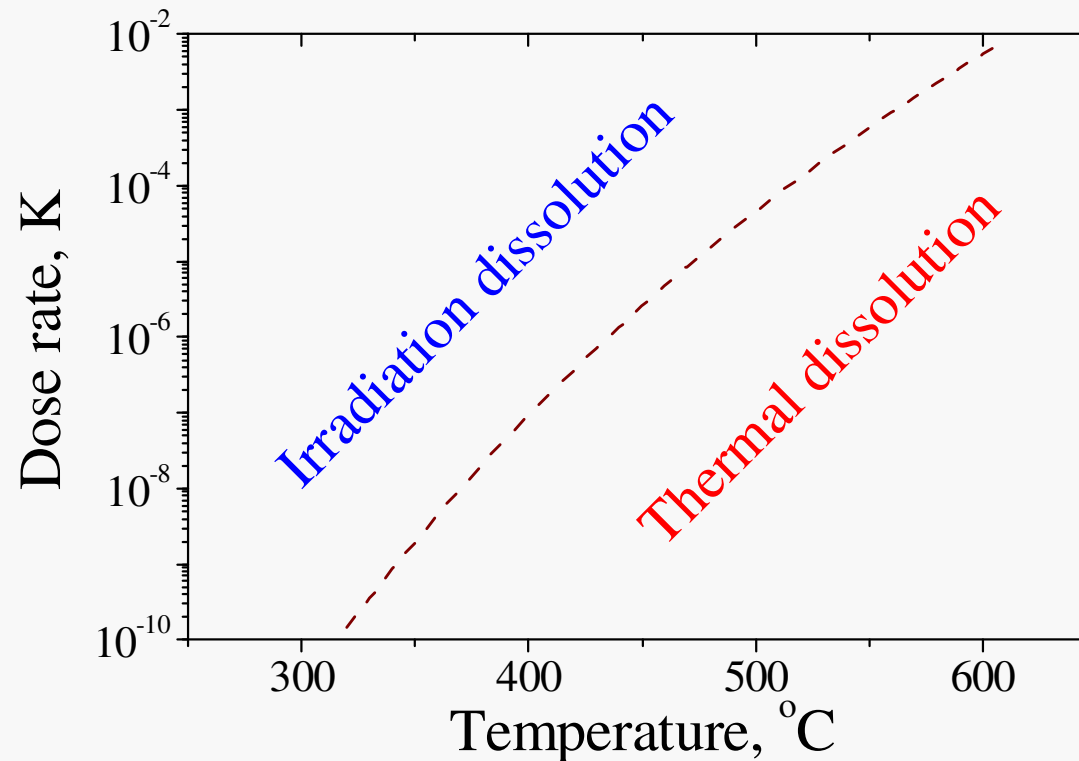
Fluxes of the radiation-emitting and thermal vacancies:

$$J_v^{irr} \approx \pi K_0 \frac{R^2 \Delta^2}{R + \Delta} \quad J_v^{th} = 4\pi R D_v C_v^0 \exp(2\gamma/R) \quad \gamma = \sigma\omega/kT$$

Effective vacancy concentration at void under irradiation:

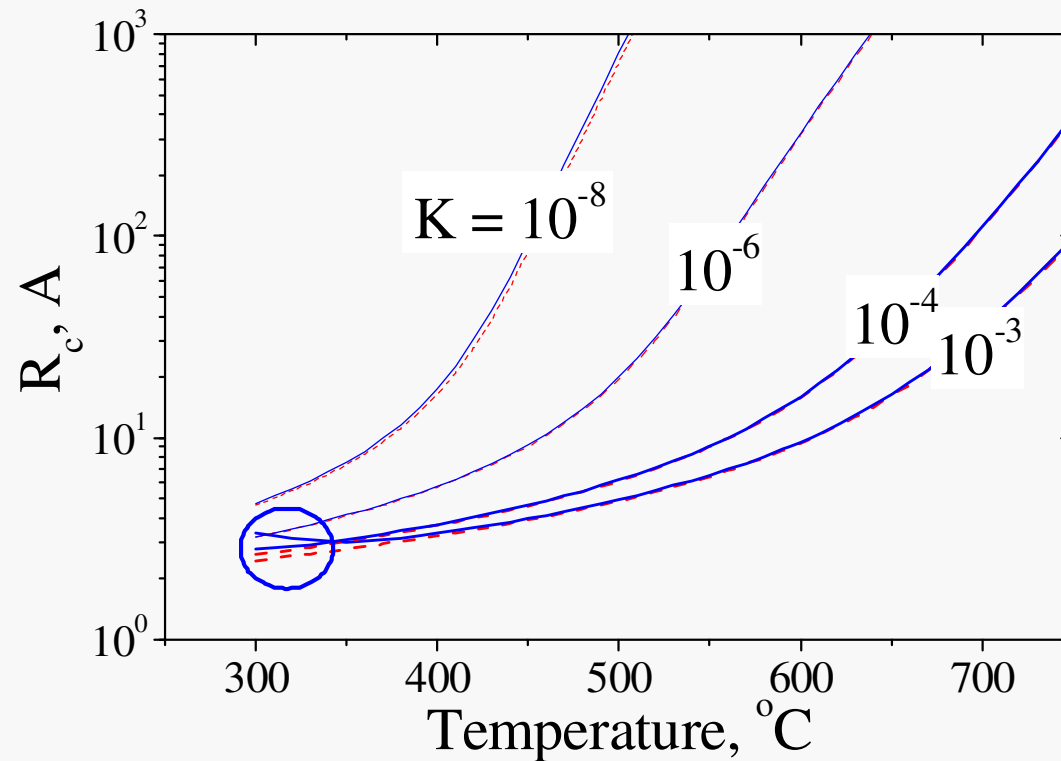
$$C_v^b \rightarrow \tilde{C}_v^b = C_v^0 \exp(2\gamma/R) + \frac{R\Delta^2 K_0}{4D_v(R + \Delta)}$$

## Void dissolution rate due to radiation or thermal vacancies



The rate of radiation-induced void shrinkage is proportional to the dose rate  $K_0$  and it is expected to increase with increasing range of focusing collisions as irradiation temperature decreases.

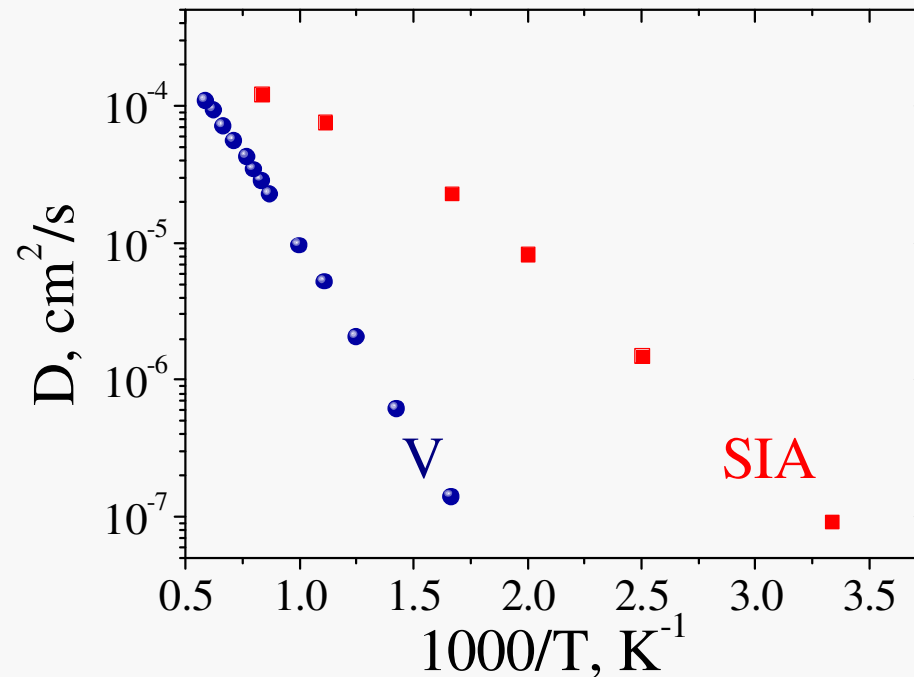
# Critical size of a void vs temperature and dose rate



*Radiation dissolution appreciably increase the critical size only at low temperatures and high dose rates.*



## Diffusion and primary damages in Fe



Migration energy of vacancy diffusion  $E_v^m = 0.58 \text{ eV}$

and of SIA diffusion  $E_i^m = 0.28 \text{ eV}$

The size of simulated box  $L$  has to be much larger than diffusion range:  $L^2 \gg 6D_i t_s$ , where  $t_s \sim 100 \text{ ps}$



# Primary damages in displacement cascades

$$N = 10^5 - 2 \cdot 10^6$$

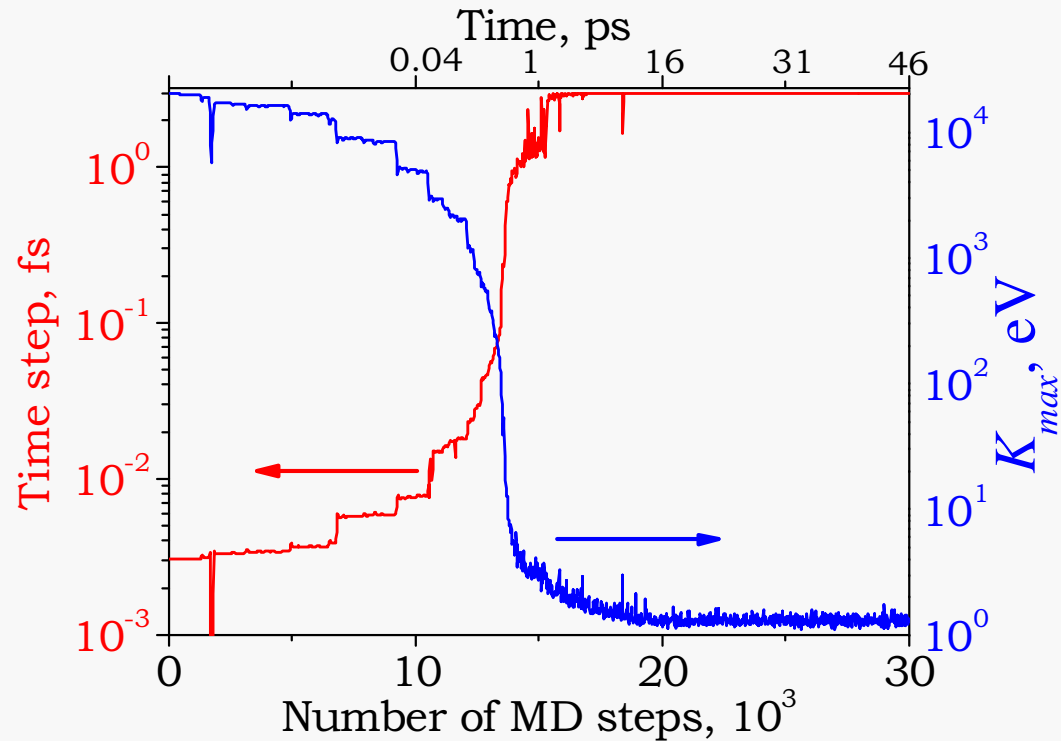
PKA energies: 0.01 – 20 keV

Temperatures: 300, 600, 900 K

Cascades at every point ( $E_d$ , T): > 50

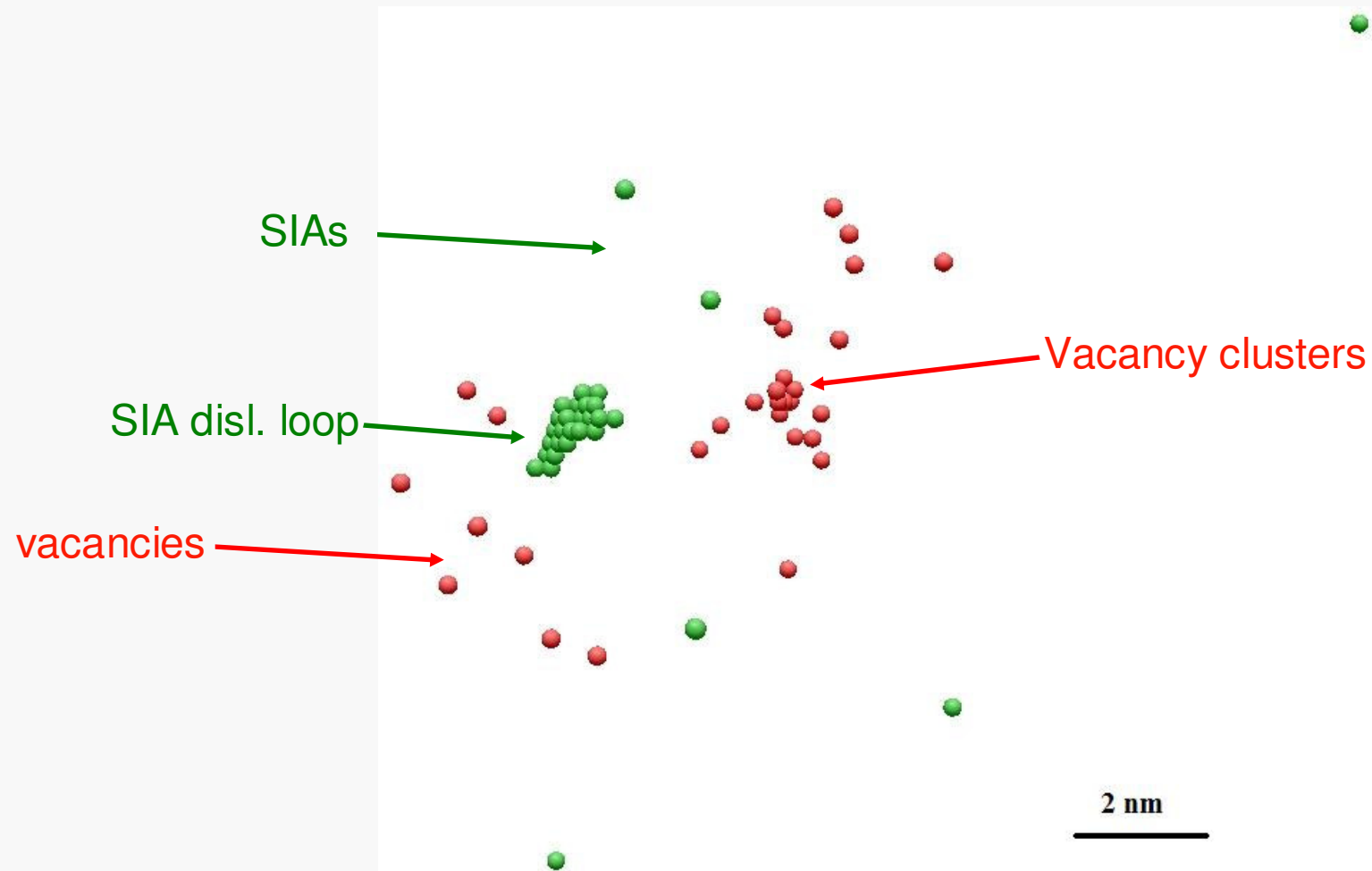
Total number of cascades: > 5000

# Variable time step. $E_{PKA} = 20$ keV, $T = 900$ K



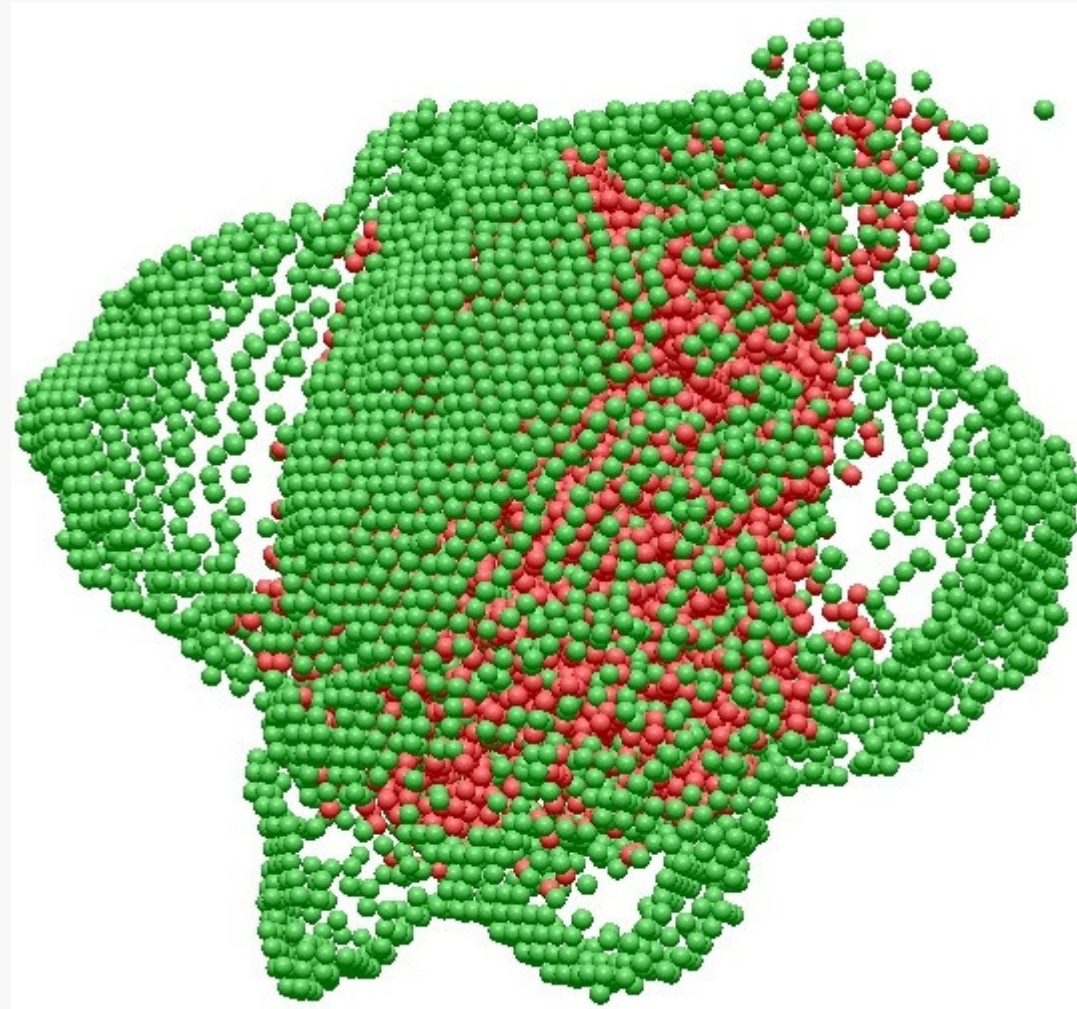
*A typical evolution of the time step and energy of fastest atom. Ballistic stage of cascade development runs out in about 1 ps.*

# Point defect distribution, $E_{\text{PKA}} = 20 \text{ keV}$ , $T = 900 \text{ K}$



# Cascade evolution in time. 1 frame per 500 MD time steps

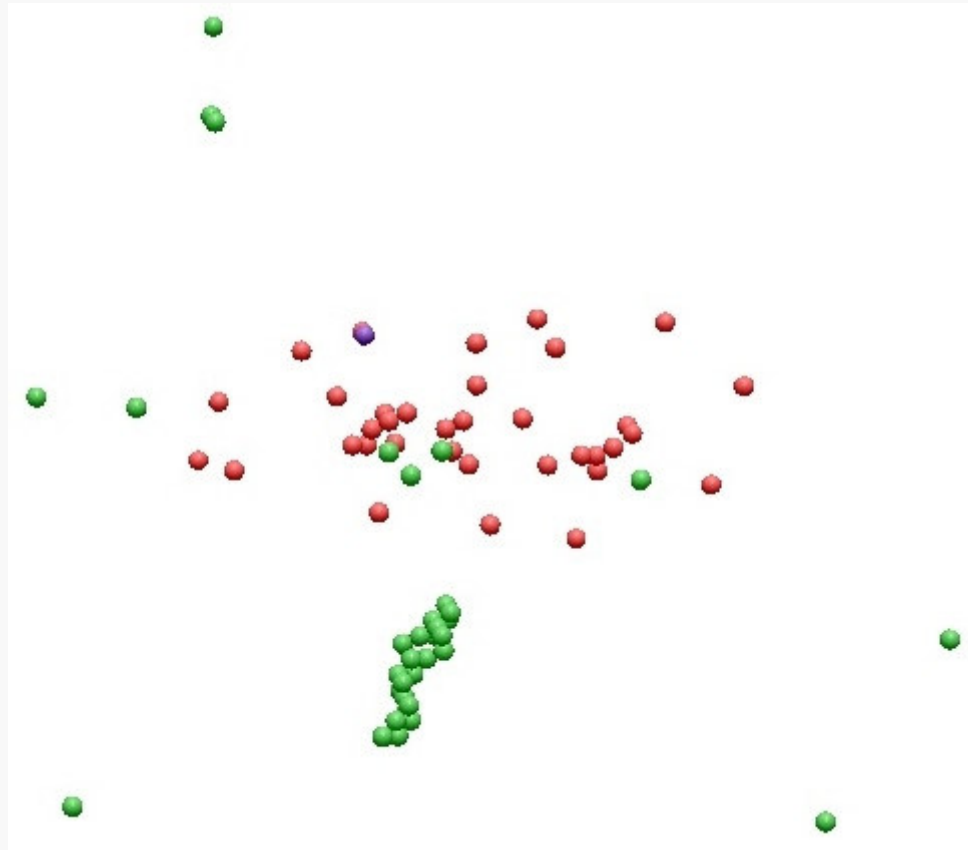
$E_{\text{PKA}} = 20 \text{ keV},$   
 $T = 900 \text{ K}$



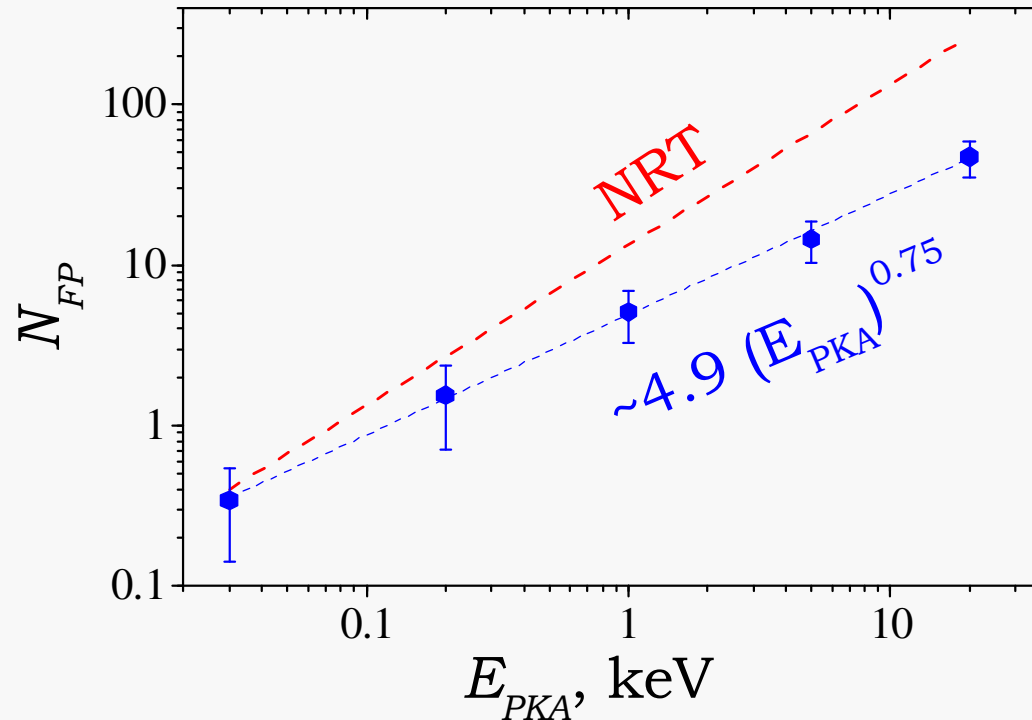


## Cascade evolution in time, another view

$E_{\text{PKA}} = 20 \text{ keV},$   
 $T = 900 \text{ K}$



# Defect production in perfect crystal at $T = 300\text{K}$

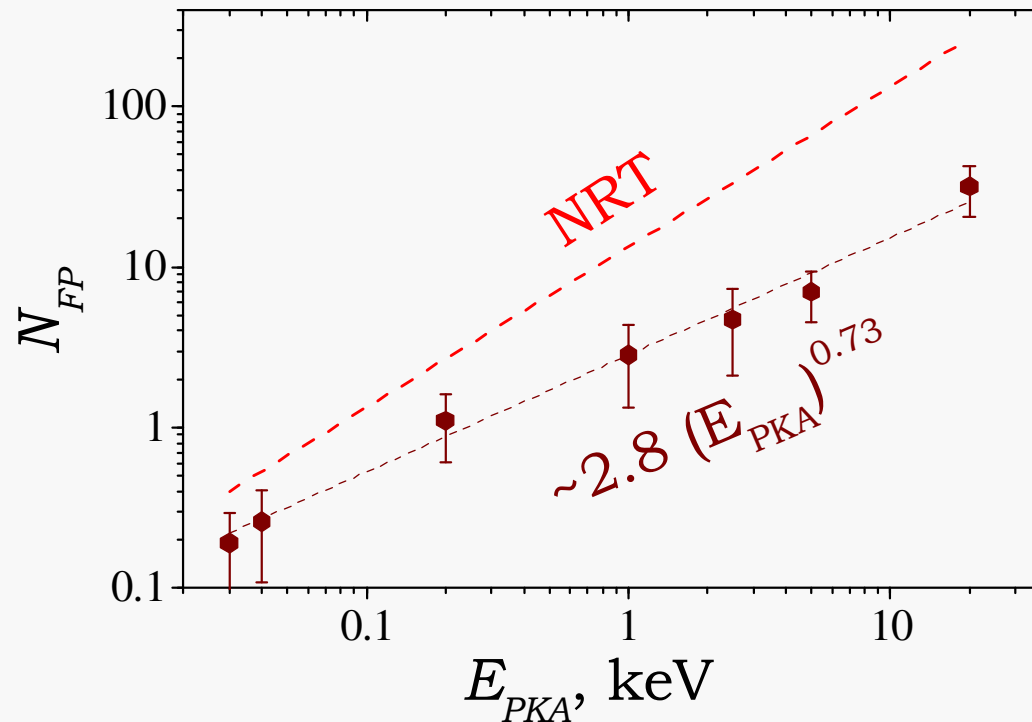


*The standard Norgett-Robinson-Torrens (NRT) theory:*

$$N_{NRT} = 0.8 E_D / 2E_d$$

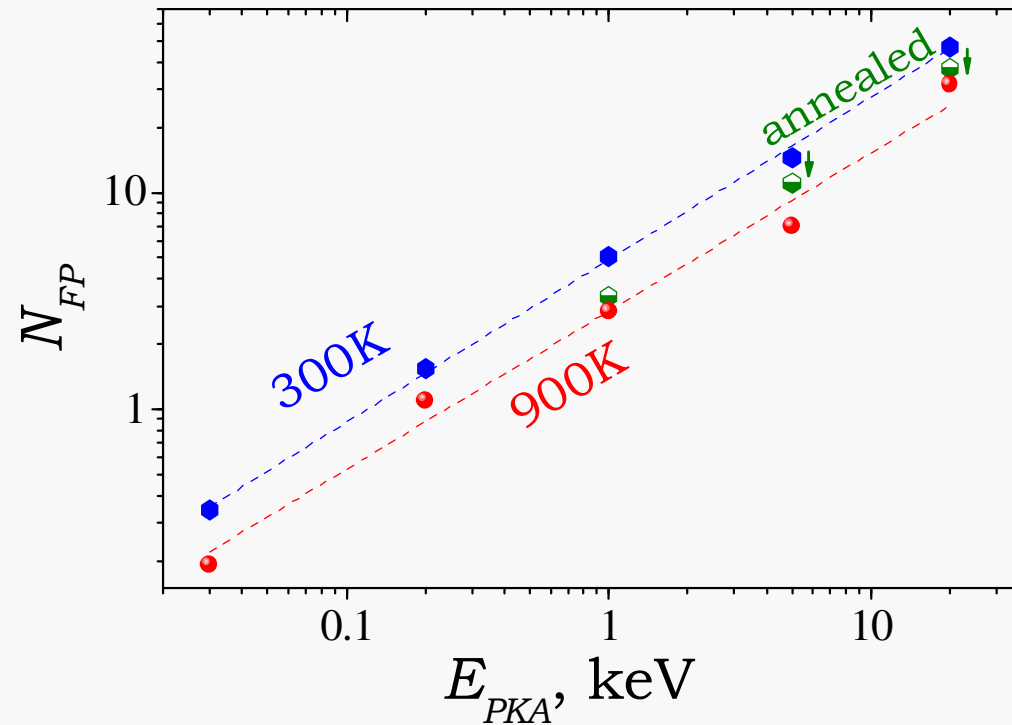
*For simulated Fe we estimate threshold energy  $E_d = 30\text{ eV}$*

# Number of Frenkel pairs vs. PKA energy at $T = 900\text{K}$



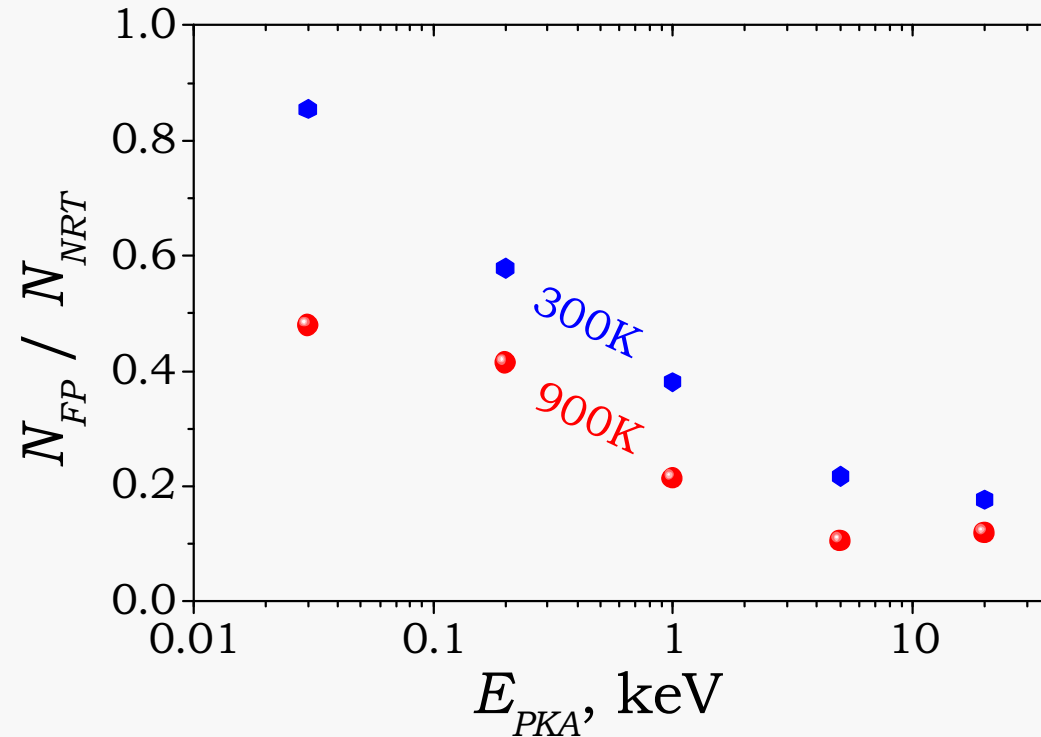
*The number of the survived point defects decreases when the temperature rises. One can expect the reduction of the effective volume of a cascade and the increase of the lifetime of the thermal spike at high temperature. Both factors enhance the recombination of defects.*

# Effect of cascade defects annealing at high temperature



*Annealing of low temperature cascade defects smoothes over the temperature effect*

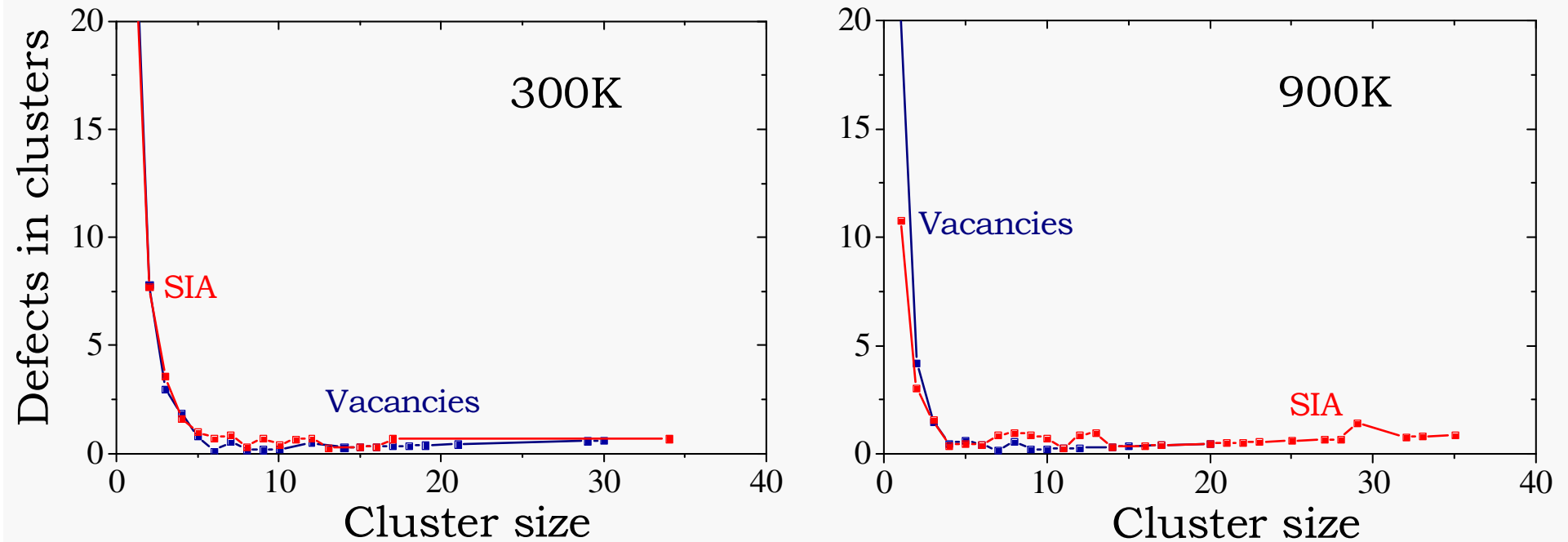
# Survived point defects fraction



*Damage production efficiency is degraded with increase of cascade energy*

# Distribution of cluster sizes

20 keV



*Both vacancies and especially SIAs tend to aggregation with the growth of temperature*



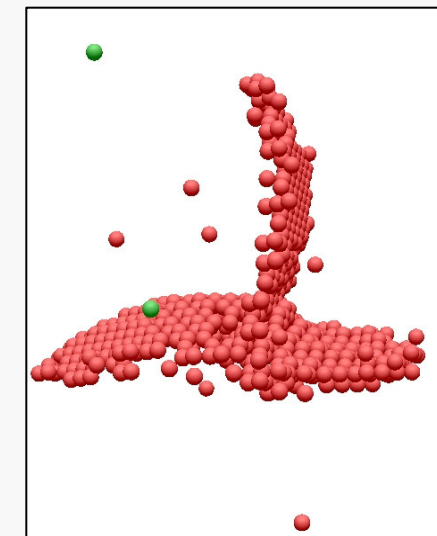
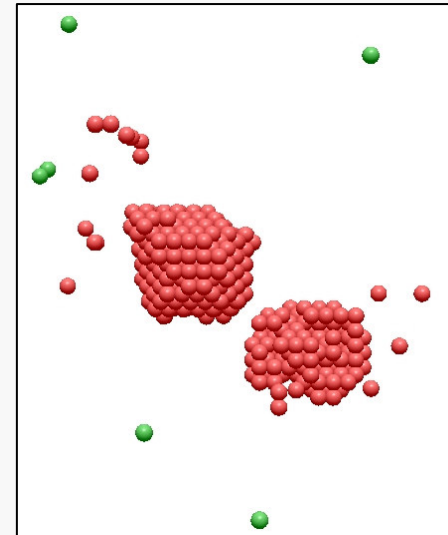
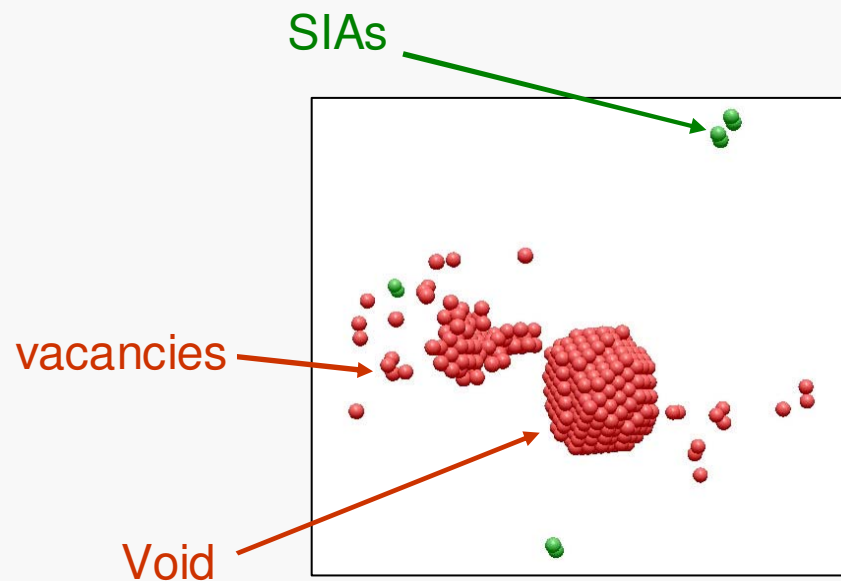
# Defects production near voids

$$N = 10^5 - 2 \cdot 10^6$$

PKA energies: 1 – 20 keV

Sizes of voids: 312 - 1004  $v_a$

# Some final states of cascade development near voids

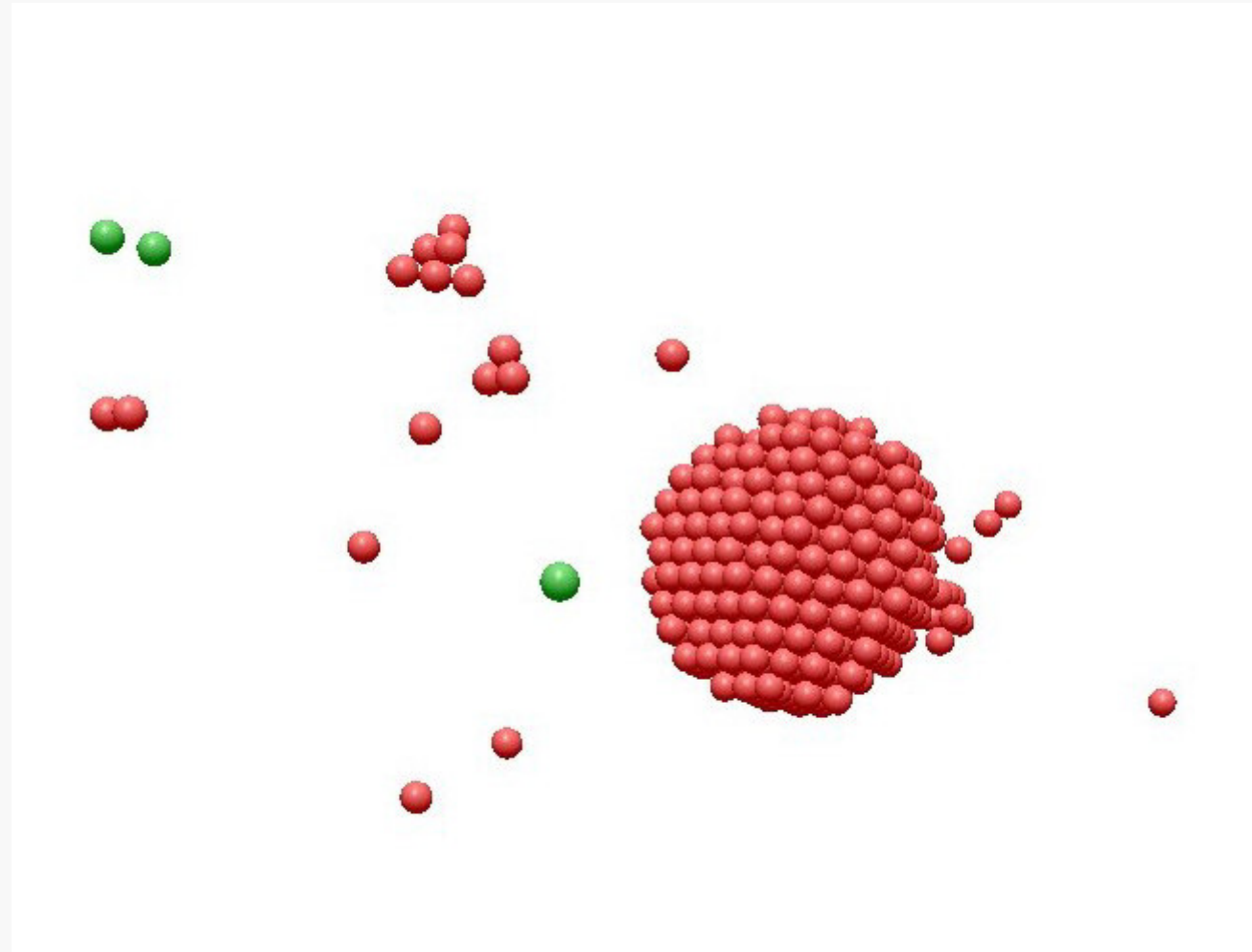


$$E_{PKA} = 8 \text{ keV}, T = 900 \text{ K}$$



Cascade evolution near a void. 1 frame per 500 MD time steps

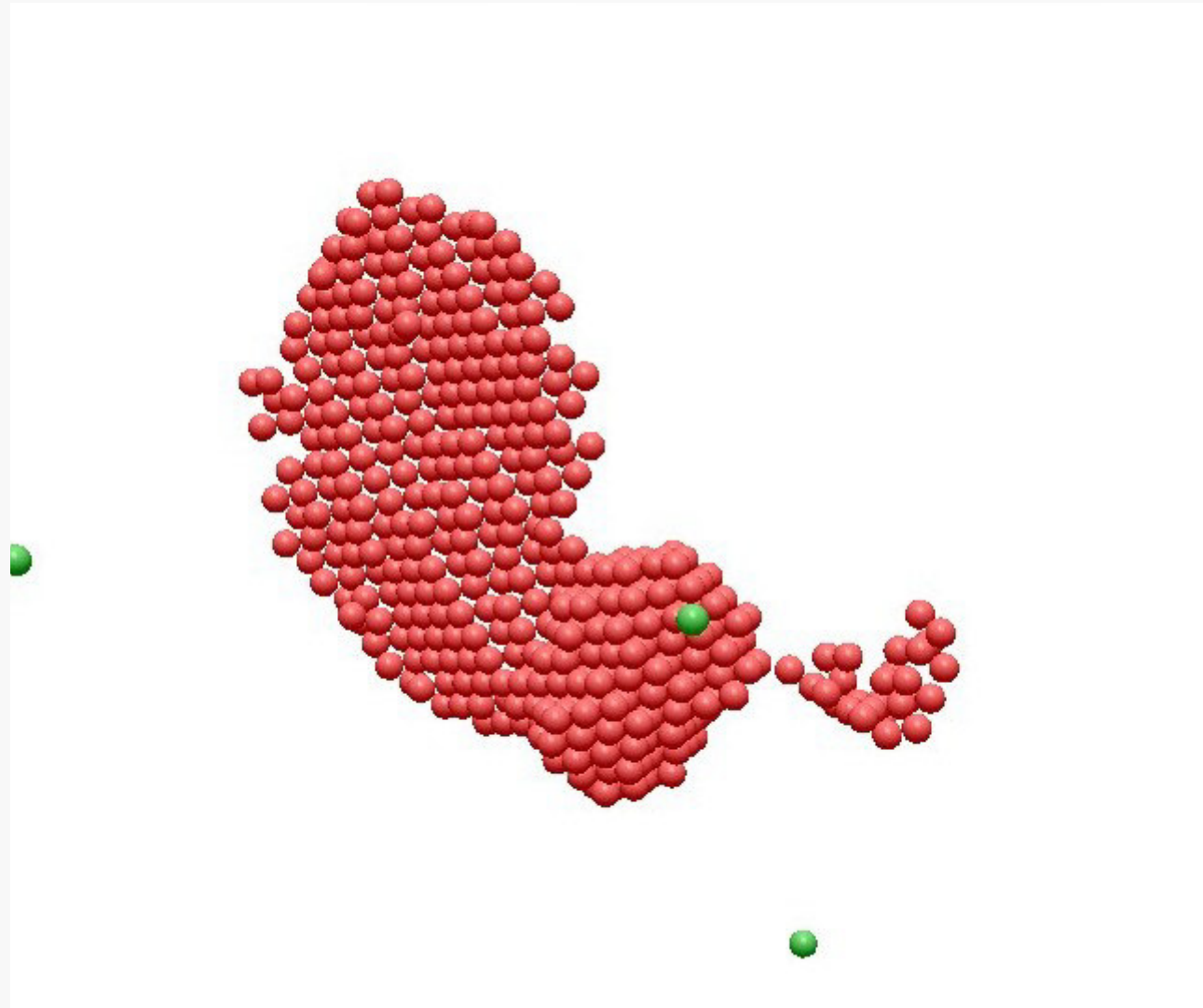
$$E_{\text{PKA}} = 8 \text{ keV}, T = 900 \text{ K}$$



# Cascade evolution near void. 1 frame per 500 MD time steps

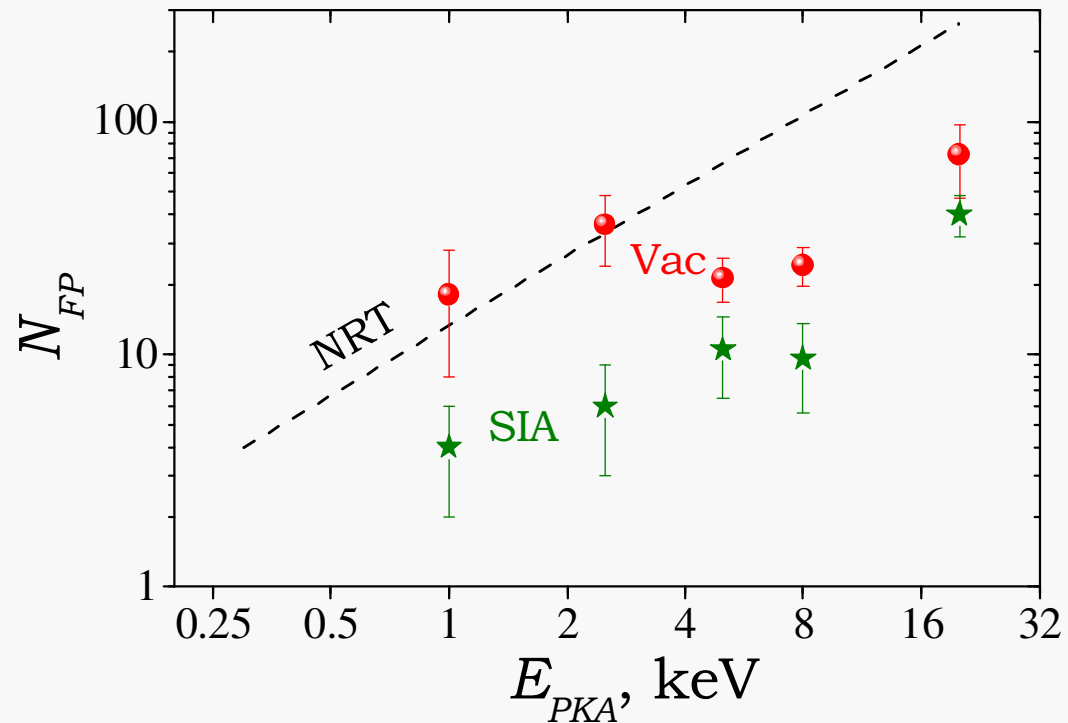
$$E_{\text{PKA}} = 8 \text{ keV}$$

$$T = 600 \text{ K}$$



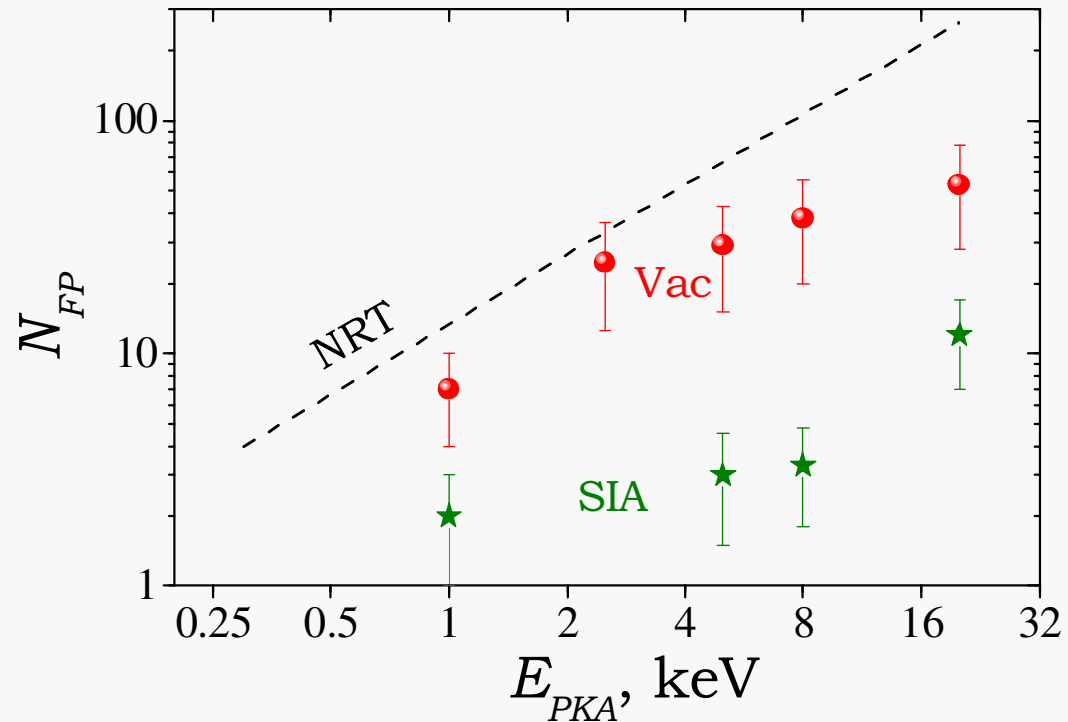
*Destroying of void by nearby cascade*

# Defect production near voids at $T = 300\text{K}$



*Biased creation of vacancies compared to interstitials is observed for all studied energies*

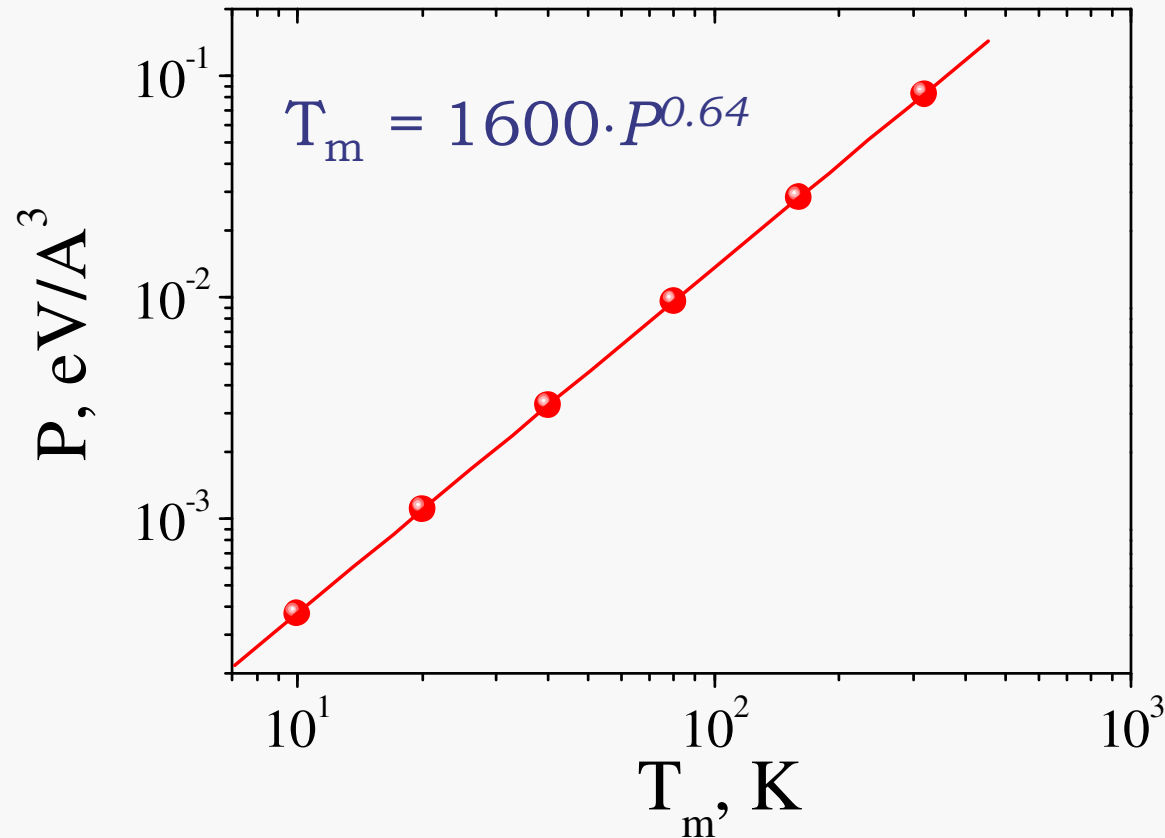
# Defect production near voids at $T = 900\text{K}$



*Effect of preferential creation of vacancies is enhanced at high temperature*



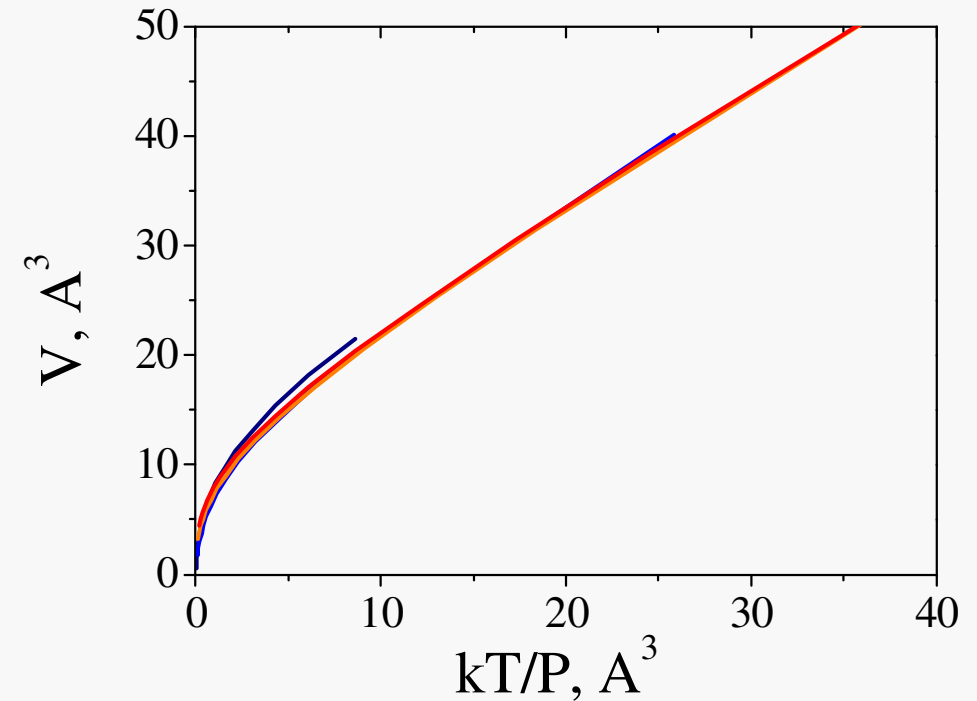
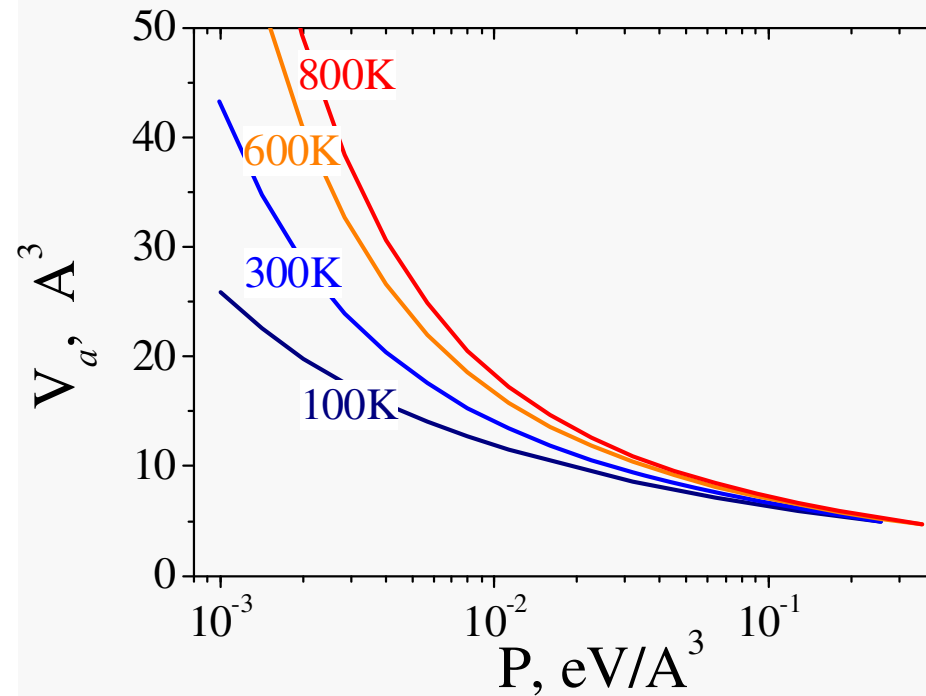
# Melting temperature of He vs pressure



*The melting temperature is found by studying the equilibrium of coexistence of liquid and crystalline phases.*

*At  $P = 0.1 \text{ eV}/\text{\AA}^3 = 16 \text{ GPa}$ , the  $T_m > 300 \text{ K}$  and it should be expected that helium can be found in bubbles exactly in solid state. Even at high temperature the helium in the bubbles is in a liquid state.*

# Equation of state for Helium



$$PV/kT = f(V)$$

*Balescu R., Equilibrium and non-equilibrium statistical mechanics, 1975*



# Defects production near He bubbles

$$N = 10^5 - 2 \cdot 10^6$$

PKA energies: 1 – 20 keV

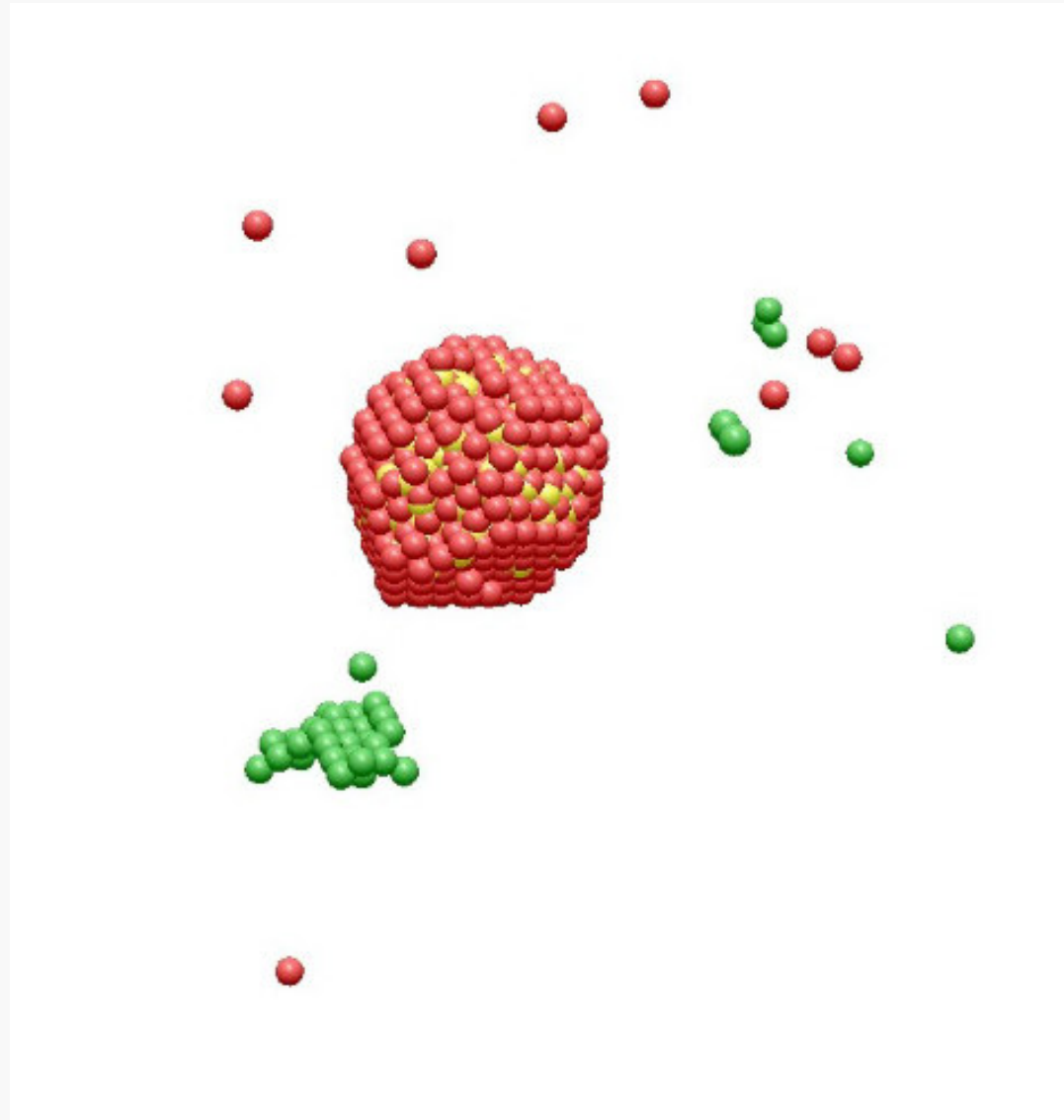
Sizes of bubbles:  $312 \nu_a$

$$\text{He}/V = 1$$

# Cascade evolution near bubble. 1 frame per 500 MD time steps

$$E_{\text{PKA}} = 8 \text{ keV}$$

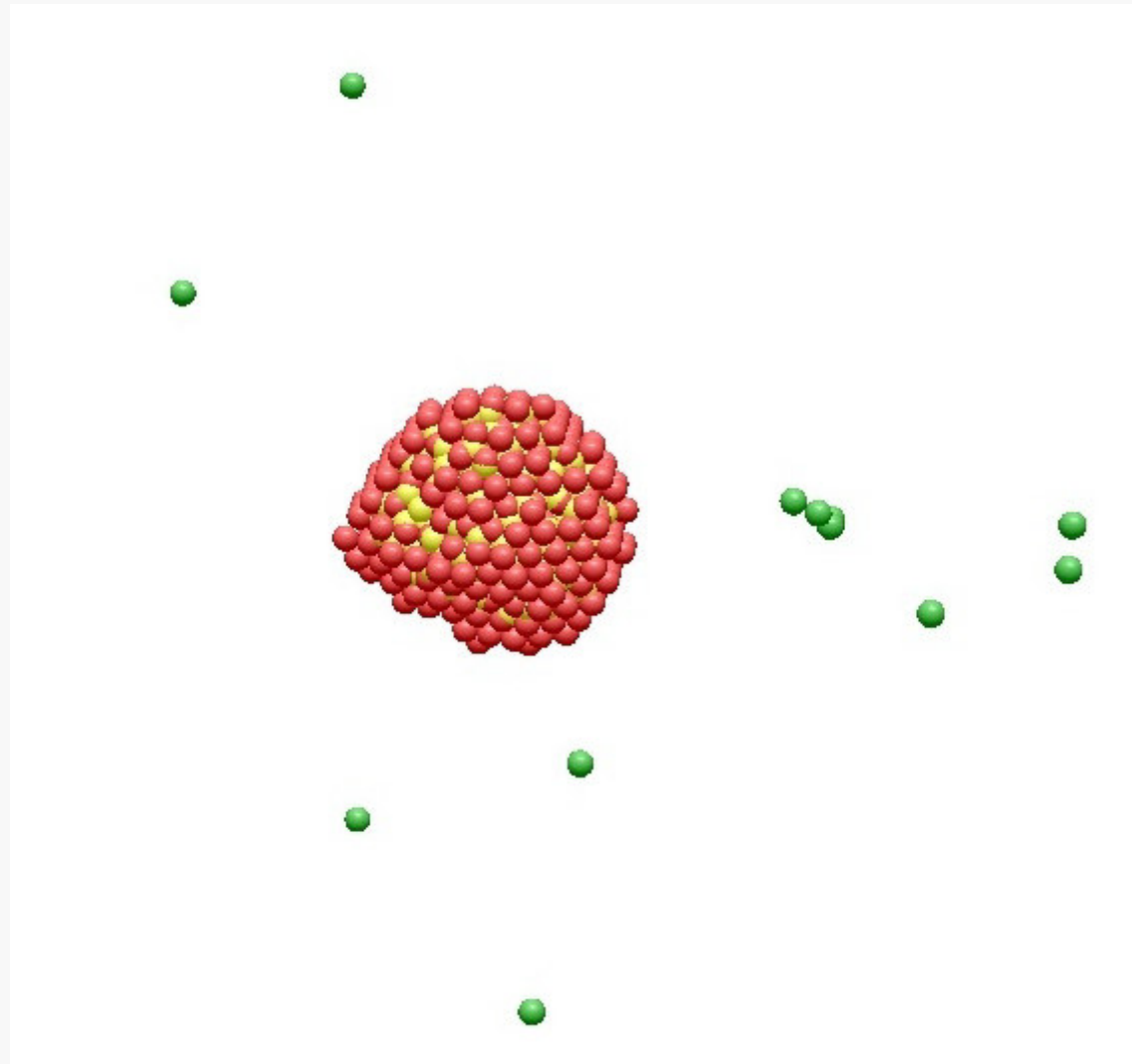
$$T = 900 \text{ K}$$



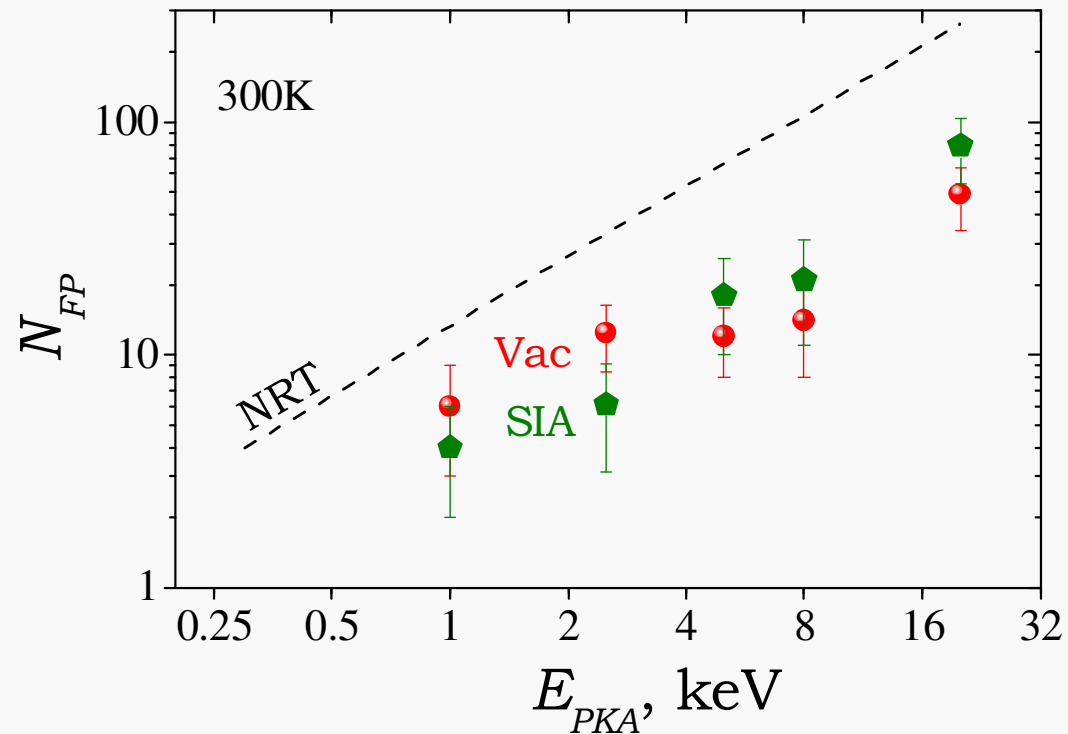


## Cascade evolution near bubble. 2-nd example

$$E_{\text{PKA}} = 8 \text{ keV},$$
$$T = 900 \text{ K}$$

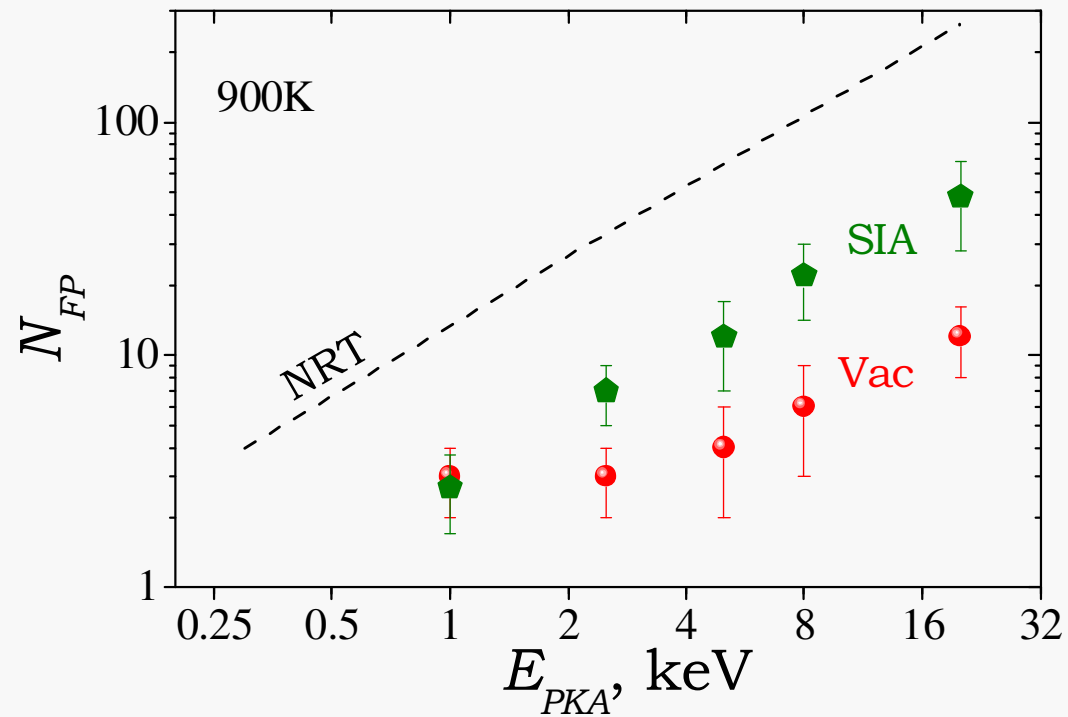


# Defect production near bubbles at $T = 300\text{K}$



*Biased creation of vacancies at low  $E_{PKA}$  and SIAs at high PKA energy*

# Defect production near bubbles at $T = 900\text{K}$



*Biased creation of SIAs at all PKA energies*

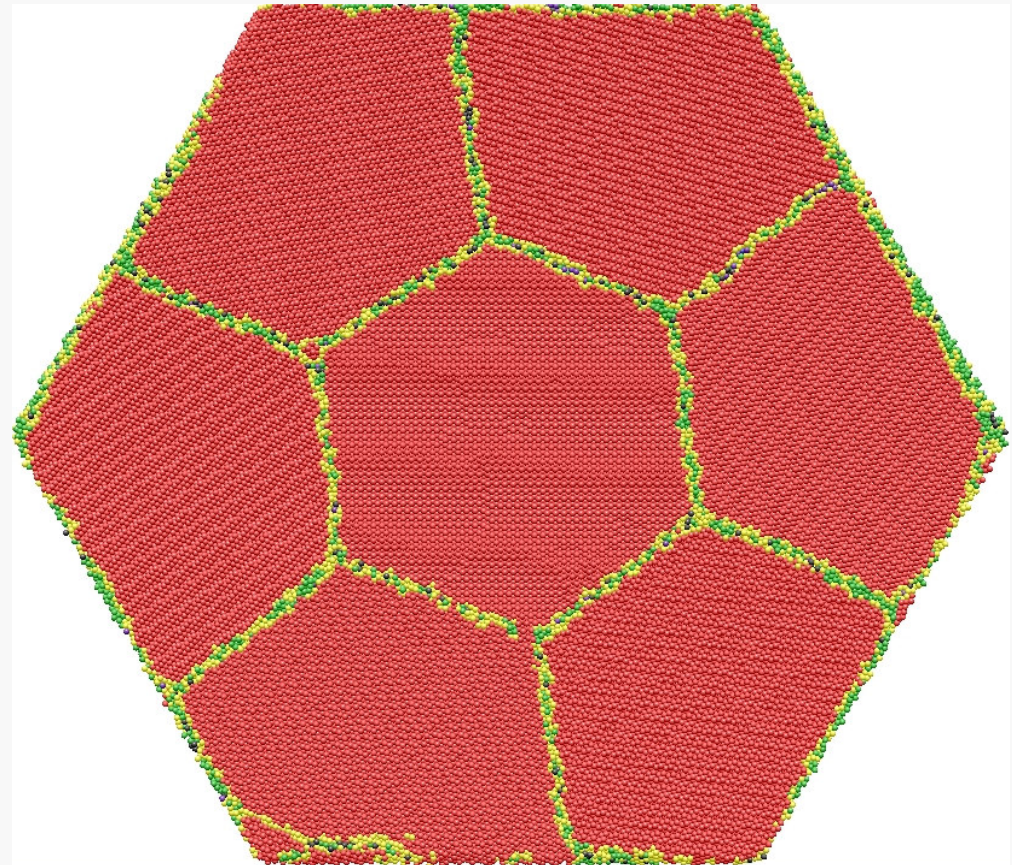
# Simulation of recrystallization under irradiation

*The polycrystal prepared by Voronoy method.*

*Number of grains is 13.*

*Total number of atoms is 3201384.*

*Mean size of the grain is 15 nm.*



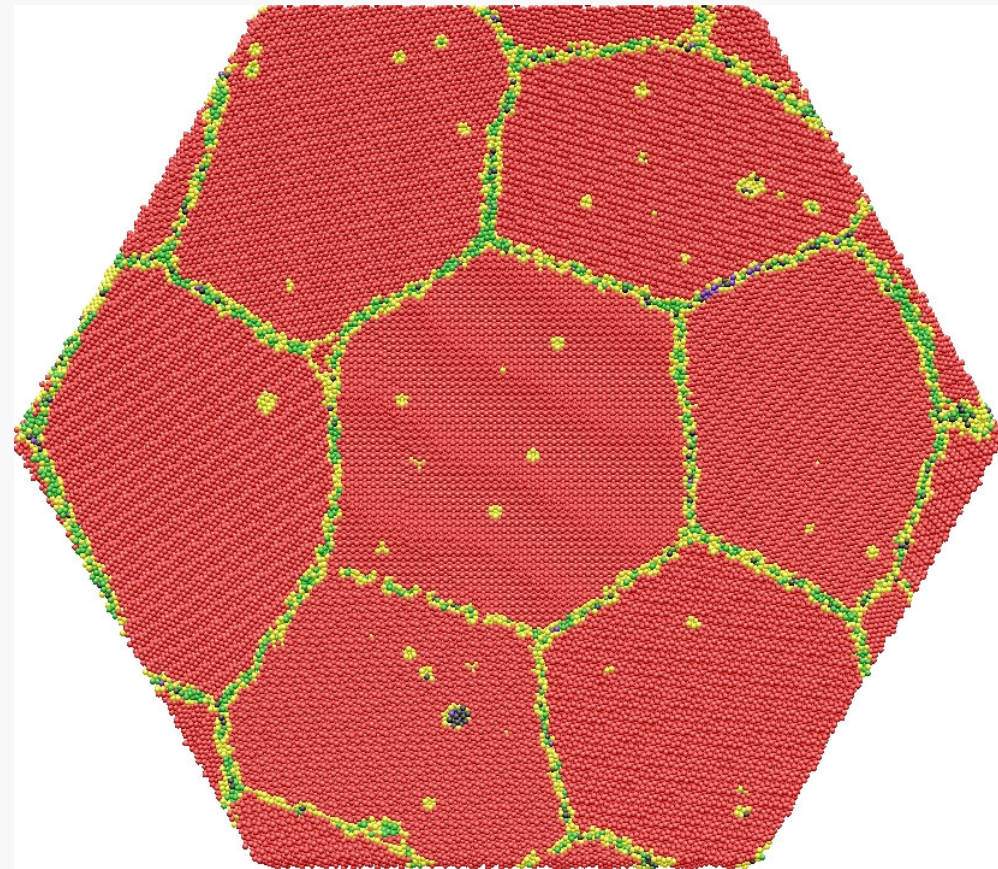
*The initial state after the high-temperature annealing. The cut of the polycrystal is taken in the central part of the cubic specimen.*

# Homogeneous irradiation of polycrystal

*A cascades with the energy 5 keV were generated every 8 ps.*

*The effective irradiation dose can be estimated as  $10^{-2}$  dpa.*

*The most part of created defects are vacancies and vacancy clusters (voids).*



*The polycrystal state after homogeneous irradiation by 800 cascades with*

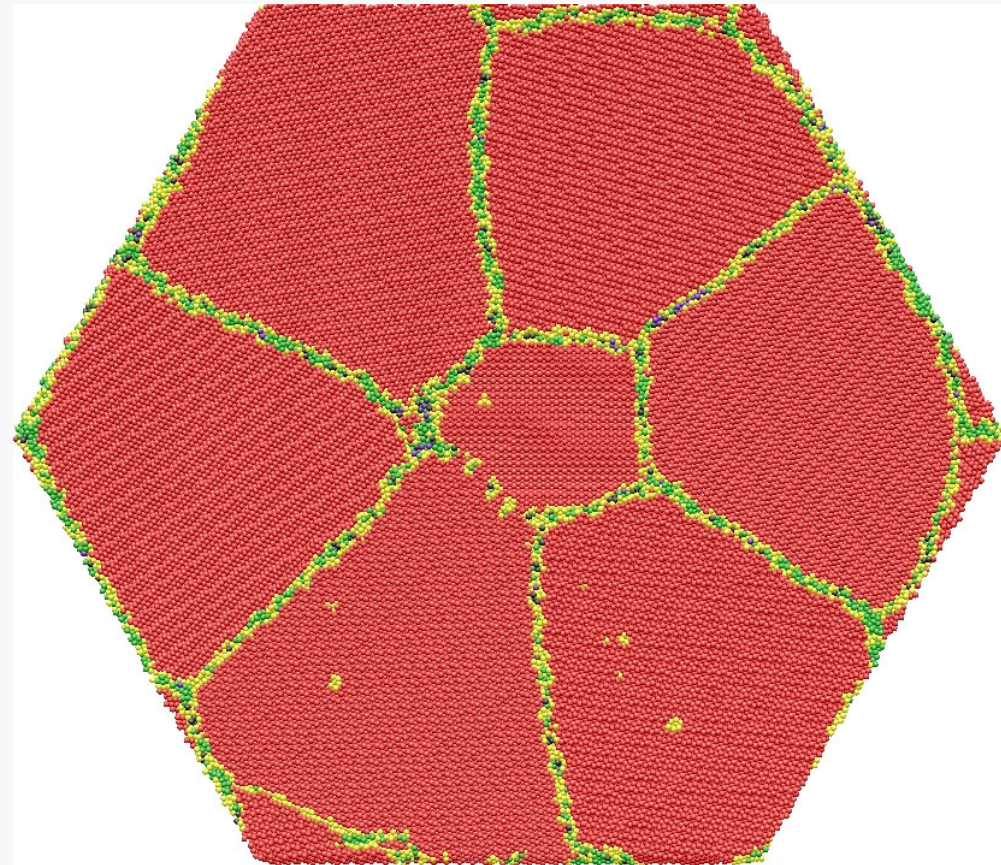
$$E_{PKA} = 5 \text{ keV at } T = 900\text{K}$$

# Heterogeneous irradiation of polycrystal

*A cascades with the energy 8 keV were generated every 15 ps.*

*The location of the PKA was in the region nearby the central grain.*

*Effective dose rate about  $3 \cdot 10^7 \text{ s}^{-1}$ .*

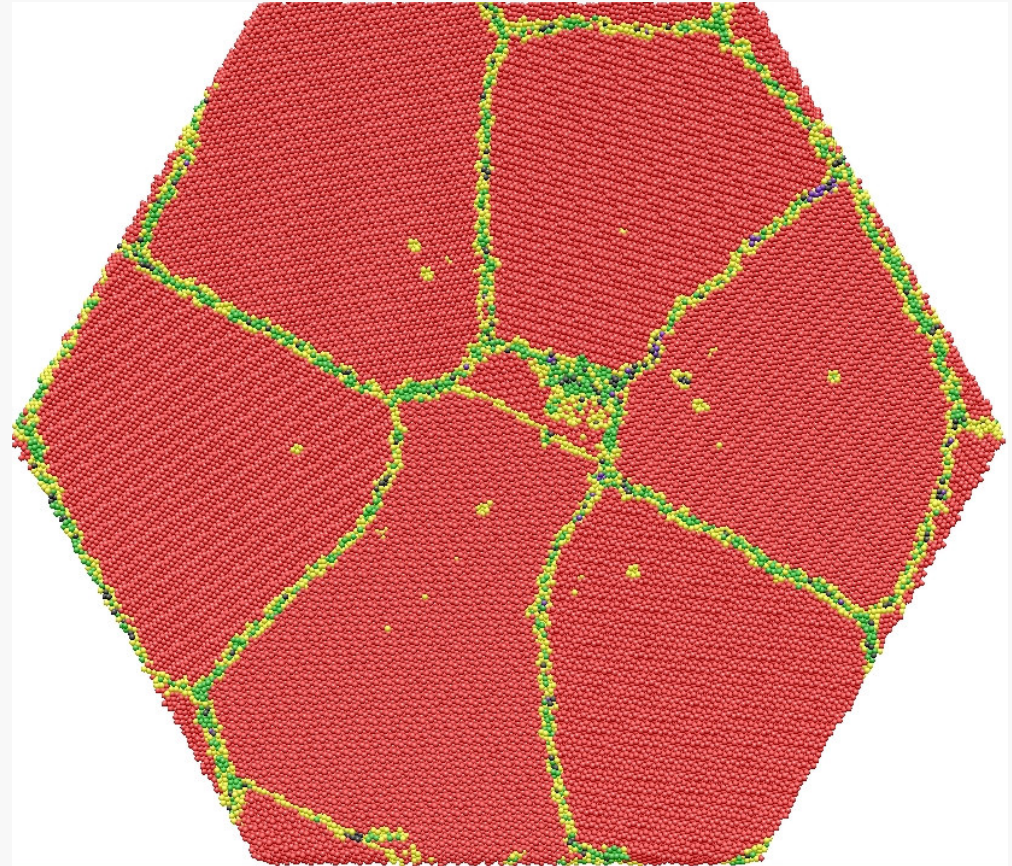


*The polycrystal state after heterogeneous irradiation by 160 cascades with  $E_{PKA} = 8 \text{ keV}$  at  $T = 900\text{K}$*

# Heterogeneous irradiation of polycrystal

*The dissolution of the central grain was observed*

*Effective irradiation dose of the central zone was about 0.15 dpa.*



*The polycrystal state after heterogeneous irradiation by 350 cascades with  $E_{PKA} = 8$  keV at  $T = 900$  K*



# Conclusion

- *Biased creation of vacancies near the voids is observed both for low energy and high energy cascades.*
- *The defect formation in the vicinity of the helium bubbles shows the opposite picture namely the preferential formation of the interstitial atoms.*
- *The impact of heterogeneous irradiation on recrystallization processes in nanosize polycrystal is observed*